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ECLinPS Plus™ SPICE Modeling Kit

Prepared by:
Senad Lomigora, Paul Shockman
ON Semiconductor Broadband Applications Engineering



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APPLICATION NOTE

Objective

The objective of "AND8009 ECLinPS Plus SPICE Modeling Kit" is to provide sufficient circuit schematic and SPICE parameter information to allow system level interconnect modeling of the ECLinPS Plus logic line devices. The kit is not intended to provide sufficient information to perform whole device logic modeling.

Schematic Information

The kit contains representative input and output schematics, netlists, and waveforms used for the ECLinPS Plus devices. The buffer, package, and ESD subcircuit models may be connected to simulate driver and receiver interconnect characteristics as shown in Figure 1. A specific device may be modeled as shown in Figure 2. No Function Logic modeling is provided.

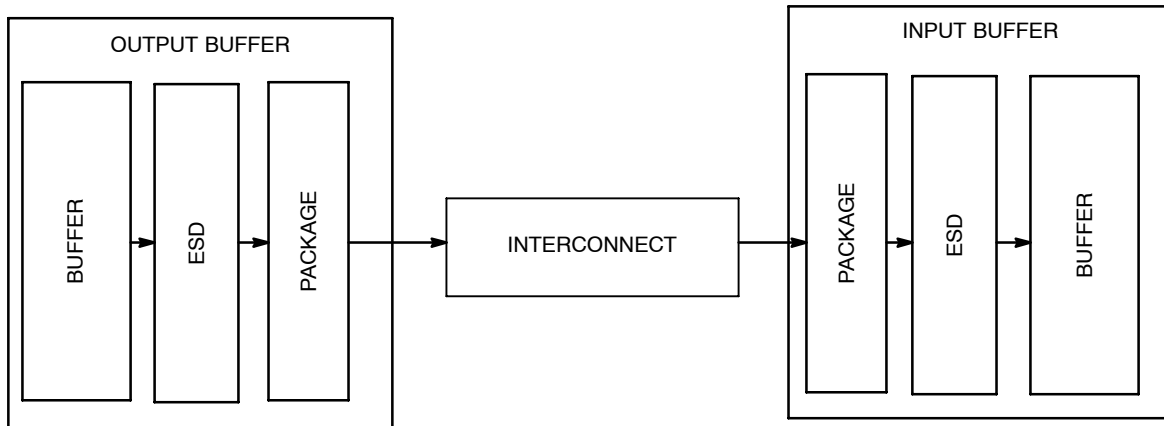


Figure 1. Interconnect Model Template

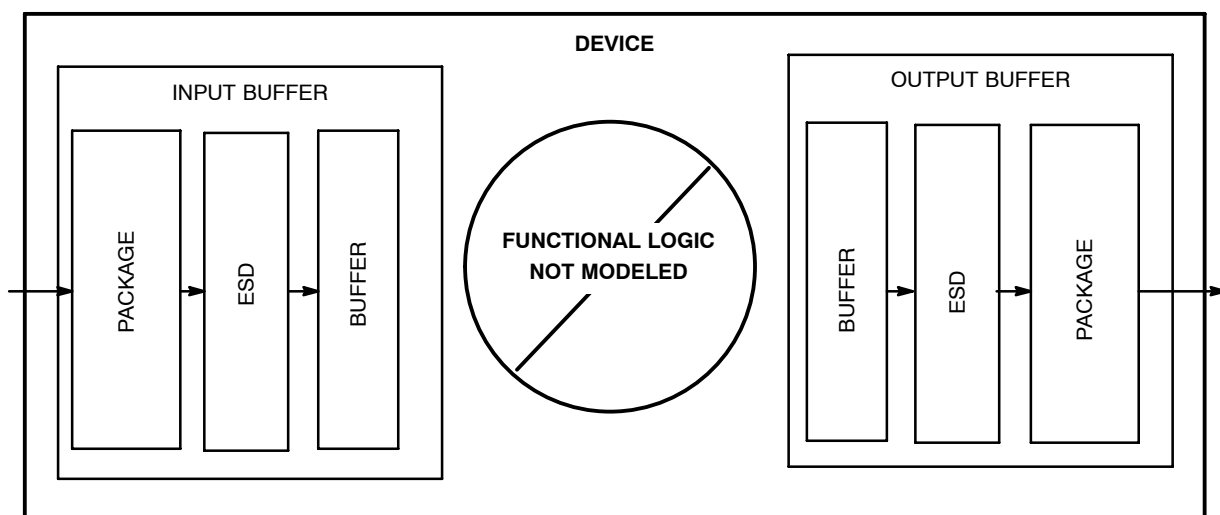


Figure 2. DEVICE Model Template

There are four terminals on all transistor models: Emitter, Base, Collector, and Substrate (biased to V_{EE}). It should be noted that circuits can be used single ended by replacing INB with V_{BB} . Table 1 describes the nomenclature used in the schematics and netlists.

To simulate a different operating modes all levels, except V_{CS} , are adjusted with respect to V_{CC} . The V_{CS} is adjusted with respect to V_{EE} ($\approx V_{EE} + 1.1 \text{ V} \pm 50 \text{ mV}$)

Table 1. Schematics and Netlist Nomenclature

Parameter	Function Description
V_{CC}	3.3 V FOR LVPECL OR (0 V) FOR LVECL
V_{CCO}	1.6 V - 2.0 V HSTL Output Positive Supply
V_{CS}	Internal Reference Voltage ($\approx V_{EE} + 1.1 \text{ V} \pm 50 \text{ mV}$)
V_{HSTL}	HSTL Internal Constant Voltage Source
V_{EE}	-3.3 V FOR LVECL OR (0 V) FOR LVPECL
GND	0 V
V_{TT}	$V_{CC} - 2 \text{ V}$ TERMINATION PLANE
IN	TRUE INPUT TO CKT
INB or $\overline{\text{IN}}$	INVERTED INPUT TO CKT
Q	TRUE OUTPUT OF CKT
QB or $\overline{\text{Q}}$	INVERTED OUTPUT OF CKT

Input Buffer

A typical input buffer schematic (Figure 3) and netlist are representing structures currently in use on most existing devices in this family. Specific devices may have unique input buffer models per Table 2. The ESD and package models should be added for more accurate model behavior. An internal input pulldown resistor is shown in the ESD network, Figure 26. Some devices may also display an internal pullup resistor to V_{CC} . Refer to specific device data sheet pinout and logic diagram for internal input resistor. The input buffers may be shown as differential, but may be modified to represent a single-ended structure by using a DC bias on the non driven input (at the signal pin common mode voltage). It is unnecessary to include an ESD or package model for the V_{BB} pins of the models because V_{BB} is intended as an internal node for most applications. If V_{BB} is modeled as an external node it is usually bypassed because it is a constant voltage, and adding ESD and Package parameters provide no additional benefit.

Output Buffer

An output buffer schematic and netlist may or may not require the temperature compensation (TC) network structure depending on the specific device series. All 100 series devices will require the TC network. A 10 series device does not include a TC network. ESD, package, and

termination models must be added for proper buffer behavior. Output buffers are shown as differential. When simulating a single-ended output, both differential outputs should utilize ESD, package, and termination models to maintain properly balanced loading.

Package

Various simplified input and output package case models may be found in the Appendix Section, Package RLC. Specific device package pin models may be modified according to IBIS model parasitics values.

EP16 Buffer Model

The EP16 interconnect has been completely modeled to provide a working schematic and output waveforms as examples of the ECLinPS Plus line. The typical input buffer may be driven with the output buffer, OBUF01. (See Figure 28, simplified EP16 SPICE model and Figure 29 typical output waveform.)

SPICE Netlists

The netlists are organized as a group of subcircuits. In each subcircuit model netlist, the model name is followed by a list of external node interconnects.

Temperature Compensation Network for 100EP

The output netlists include temperature compensation network circuitry for 100EP style output buffers. The circuit components of the temperature compensation networks are shown in Figure 29. For simulating 10EP style outputs these components should either be deleted or commented out of the subcircuit netlists. Subcircuit models such as the Input or Output Buffer, Package, Input ESD and Output ESD should connect to supplies through hierarchical, passed parameters such as V_{CC} , V_{EE} , etc., for proper simulation and not separately attached to independent power supplies.

SPICE Parameter Information

In addition to the schematics and netlists is a listing of the SPICE parameters for the transistors referenced in the schematics and netlists. These parameters represent a typical device of a given transistor. Varying the typical parameters will affect the DC and AC performance of the structures; but for the type of modeling intended by this note, the actual delay times are not necessary and are not modeled, as a result variation of the device parameters are meaningless. The performance levels are more easily varied by other methods and will be discussed in the next section. The resistors referenced in the schematics are polysilicon and have no parasitic capacitance in the real circuit and none is required in the model. The schematics display the only devices needed in the SPICE netlists.

Modeling Information

The bias drivers for the devices are not detailed since their circuitry would result in a substantial increase of model complexity and simulation time. Instead, these internal reference voltages (V_{BB} , V_{CS} , V_{HSTL} , etc.) should be driven with ideal constant voltage sources.

The schematics and SPICE parameters will provide a typical output waveshape, which can be seen in Figures 29, 30, and 31. Simple adjustments can be made to the models allowing output characteristics to simulate conditions at or near the corners of the data book specifications. Consistent cross-point voltages need to be maintained.

- To adjust rise and fall times:

Produce the desired rise and fall times output slew rates by adjusting collector load resistors to change the gates tail current. The V_{CS} voltage will affect the tail current in the output differential, which will interact with the load resistor and collector resistor to determine t_r and t_f at the output.

- To adjust the V_{OH} :

Adjust the V_{OH} and V_{OL} level by the same amount by varying V_{CC} . The output levels will follow changes in V_{CC} at a 1:1 ratio.

- To adjust the V_{OL} only:

Adjust the V_{OL} level independently of the V_{OH} level by increasing or decreasing the collector load resistance. Note that the V_{OH} level will also change slightly due to a I_{BASER} drop across the collector load resistor. V_{OL} can be changed by varying the V_{CS} supply, and therefore the gate current through the current source resistor.

Summary

The information included in this kit provides adequate information to run a SPICE level system interconnect simulation. Device input or output models are presented in Table 2. For EP and LVEP series devices not listed in Table 2, consult www.onsemi.com (Technical Support).

Table 2. ECLinPS PLUS INPUT/OUTPUT SELECTION TABLE

Device	Package A	Package B	Input ESD	Input Buffer	Output Buffer	Output ESD
EP01	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP05	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP08	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP11	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP14	20-lead TSSOP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
EP16	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP17	20-lead SO	20-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF06	OUT_ESD
EP29	20-lead TSSOP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
EP31	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP32	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP33	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF02	OUT_ESD
EP35	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP40	20-lead TSSOP	N/A	IN_ESD	TYPICAL INBUF	OBUF09	OUT_ESD
EP51	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP52	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP56	20-lead SO	20-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF04	OUT_ESD
EP57	20-lead TSSOP	N/A	IN_ESD	TYPICAL INBUF	OBUF04	OUT_ESD
EP58	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
EP89	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF05	OUT_ESD
EP90	20-lead TSSOP	N/A	IN_ESD	TYPICAL INBUF	OBUF04	OUT_ESD
EP016	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF02	OUT_ESD
EP016A	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF02	OUT_ESD
EP101	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF06	OUT_ESD
EP105	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF06	OUT_ESD
EP116	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF06	OUT_ESD
EP131	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF02	OUT_ESD

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Table 2. ECLinPS PLUS INPUT/OUTPUT SELECTION TABLE

Device	Package A	Package B	Input ESD	Input Buffer	Output Buffer	Output ESD
EP139	20-lead SO	20-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF07	OUT_ESD
EP140	8-lead SO	N/A	IN_ESD	TYPICAL INBUF	OBUF09	OUT_ESD
EP142	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
EP195	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF04	OUT_ESD
EP196	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF04	OUT_ESD
EP210S	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF10	OUT_ESD
EP223	64-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF11	OUT_ESD
EP445	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
EP446	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF04	OUT_ESD
EP451	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
EP809	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF11	OUT_ESD
LVEP11	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF08	OUT_ESD
LVEP14	20-lead TSSOP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
LVEP16	8-lead SO	8-lead TSSOP	IN_ESD	TYPICAL INBUF	OBUF08	OUT_ESD
LVEP17	20-lead TSSOP	24-lead QFN	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
LVEP34	16-lead SO*	16-lead TSSOP*	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
LVEP56	20-lead TSSOP	24-lead QFN	IN_ESD	TYPICAL INBUF	OBUF01	OUT_ESD
LVEP111	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
LVEP210	32-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
LVEP221	52-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
LVEP222	52-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
LVEP224	64-lead LQFP	N/A	IN_ESD	TYPICAL INBUF	OBUF03	OUT_ESD
NV4N840M	QFN-32	-	-	50 Ω to V_{CC}	OBUF12	-
NB4L16M	QFN-16	-	-	50 Ω to V_{CC}	OBUF14	-
NB4N527S	QFN-16	-	-	INBUF02	OBUF13	-
NB4N855S	Micro-10	-	-	INBUF02	OBUF13	-
NB4N507A	SOIC-16	-	-	INBUF04	OBUF15	-

*For package model, please consult manufacturer at www.onsemi.com (Technical Support).

Netlists and Schematics

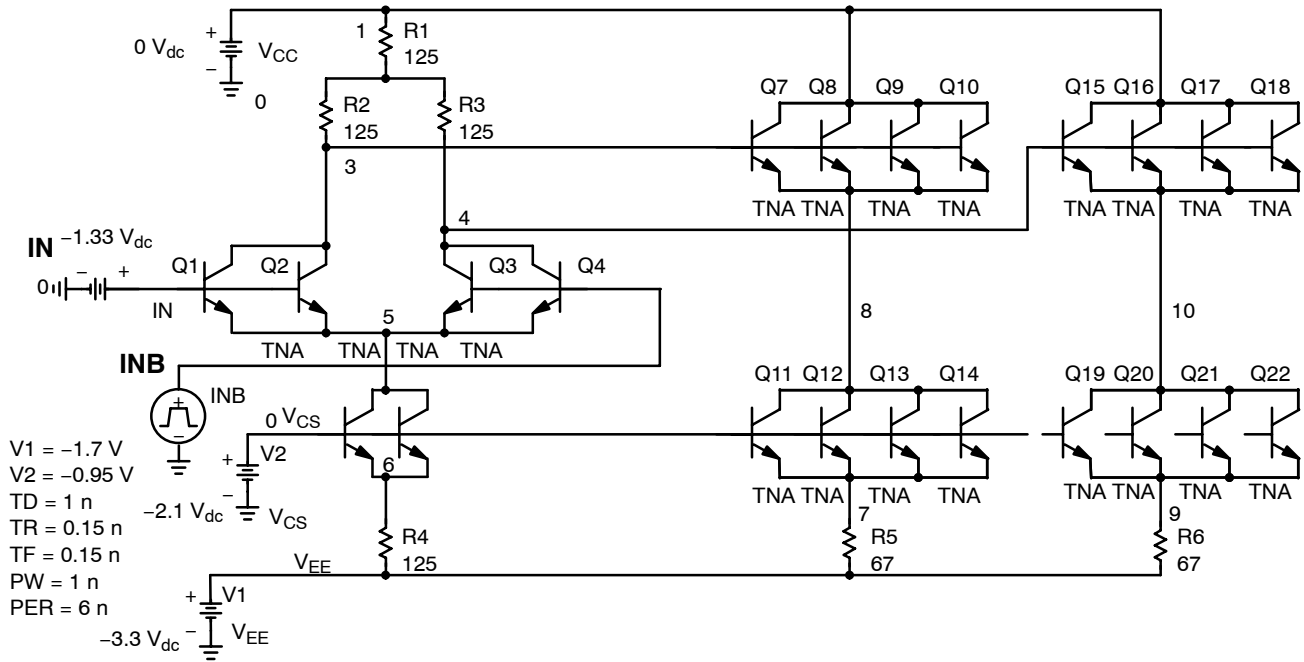


Figure 3. Typical INBUF

.SUBCKT TYPICAL INBUF IN INB VCS VEE

```

Q_Q1      3 IN 5 TNA
Q_Q2      3 IN 5 TNA
Q_Q3      4 INB 5 TNA
Q_Q4      4 INB 5 TNA
Q_Q5      5 VCS 6 TNA
Q_Q6      5 VCS 6 TNA
Q_Q7      1 3 8 TNA
Q_Q8      1 3 8 TNA
Q_Q9      1 3 8 TNA
Q_Q10     1 3 8 TNA
Q_Q11     8 VCS 7 TNA
Q_Q12     8 VCS 7 TNA
Q_Q13     8 VCS 7 TNA
Q_Q14     8 VCS 7 TNA
Q_Q15     1 4 10 TNA
Q_Q16     1 4 10 TNA
Q_Q17     1 4 10 TNA
Q_Q18     1 4 10 TNA
Q_Q19     10 VCS 9 TNA
Q_Q20     10 VCS 9 TNA
Q_Q21     10 VCS 9 TNA
Q_Q22     10 VCS 9 TNA
R_R1      2 1 125
R_R2      3 2 125
R_R3      4 2 125
R_R4      VEE 6 125
R_R5      VEE 7 67
R_R6      VEE 9 67
V_V1      VEE 0 -3.3Vdc
V_V2      VCS 0 -2.1Vdc
V_IN      IN 0 -1.33Vdc
V_VCC     1 0 0Vdc
V_INB     INB 0
+PULSE -1.7V -0.95V 1n 0.15n 0.15n 1n 6n
.END TYPICAL INBUF
    
```

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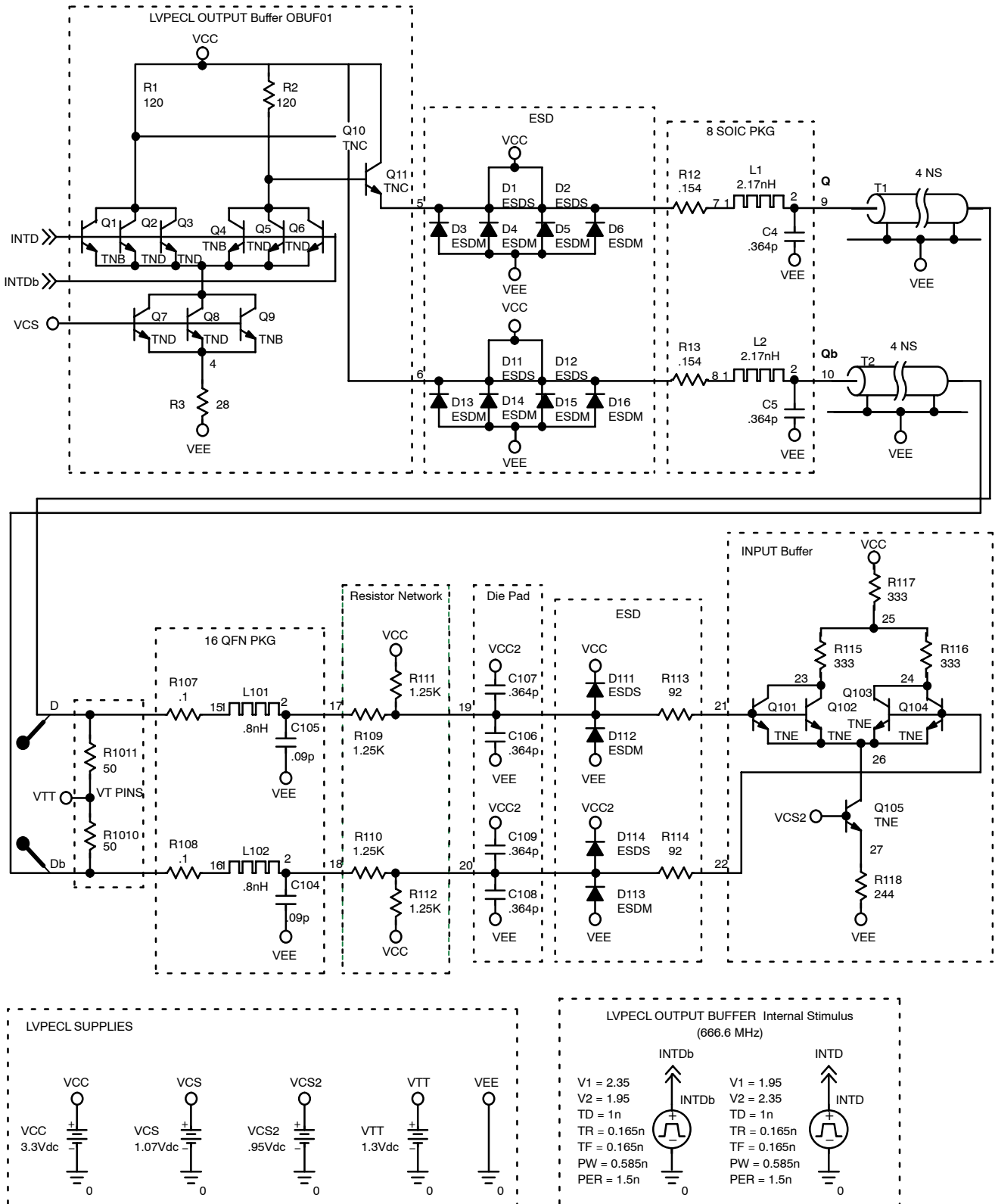


Figure 4.

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* OBUF01 driving INBUF02

```
V_INTD          INTD 0  +PULSE 2.35 1.95 1n 0.165n 0.165n 0.585n 1.5n
V_INTDb         INTDB 0  +PULSE 1.95 2.35 1n 0.165n 0.165n 0.585n 1.5n
V_VCC           $G_VCC 0  3.3Vdc
V_VCS           $G_VCS 0  1.07Vdc
V_VCS2          $G_VCS2 0  .95Vdc
V_VTT           $G_VTT 0  1.3Vdc
```

.SUBCKT OBUF01 INTD INTDb VCC VCS VEE VTT D DB

```
C_C4           0 9  .364p
C_C5           0 10 .364p
D_D1           5 $G_VCC ESDS
D_D2           5 $G_VCC ESDS
D_D3           0 5  ESDM
D_D4           0 5  ESDM
D_D5           0 5  ESDM
D_D6           0 5  ESDM
D_D11          6 $G_VCC ESDS
D_D12          6 $G_VCC ESDS
D_D13          0 6  ESDM
D_D14          0 6  ESDM
D_D15          0 6  ESDM
D_D16          0 6  ESDM
L_L1           7 9  2.17nH
L_L2           8 10 2.17nH
Q_Q1           2 INTD 1 TNB
Q_Q2           2 INTD 1 TND
Q_Q3           2 INTD 1 TND
Q_Q4           3 INTDB 1 TNB
Q_Q5           3 INTDB 1 TND
Q_Q6           3 INTDB 1 TND
Q_Q7           1 $G_VCS 4 TND
Q_Q8           1 $G_VCS 4 TND
Q_Q9           1 $G_VCS 4 TNB
Q_Q10          $G_VCC 2 6 TNC
R_R1           2 $G_VCC 120
R_R2           3 $G_VCC 120
R_R3           0 4  28
R_R12          5 7  .154
R_R13          6 8  .154
T_T1           9 0 D 0 Z0=50 TD=4000ps
T_T2           10 0 DB 0 Z0=50 TD=4000ps
.END OBUF01
```


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```
.SUBCKT INBUF02 D DB VCC VCS VEE
C_C104      0 18  .09p
C_C105      0 17  .09p
C_C106      0 19  .364p
C_C107      19 $G_VCC2  .364p
C_C108      0 20  .364p
C_C109      20 $G_VCC2  .364p
D_D111      19 $G_VCC  ESDS
D_D112      0 19  ESDM
D_D113      0 20  ESDM
D_D114      20 $G_VCC2  ESDS
L_L101      15 17  .8nH
L_L102      16 18  .8nH
Q_Q101      23 21 26  TNE
Q_Q102      23 21 26  TNE
Q_Q103      24 22 26  TNE
Q_Q104      24 22 26  TNE
Q_Q105      26 $G_VCS2 27  TNE
Q_Q11       $G_VCC 3 5  TNC
R_R107      D 15  .1
R_R108      DB 16  .1
R_R109      19 17  1.25K
R_R110      18 20  1.25K
R_R111      19 $G_VCC  1.25K
R_R112      $G_VCC 20  1.25K
R_R113      19 21  92
R_R114      22 20  92
R_R115      23 25  333
R_R116      24 25  333
R_R117      25 $G_VCC  333
R_R118      0 27  244
R_R1010     $G_VTT DB  50
R_R1011     D $G_VTT  50
.END INBUF02
```

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INBUF04 INPUT BUFFER

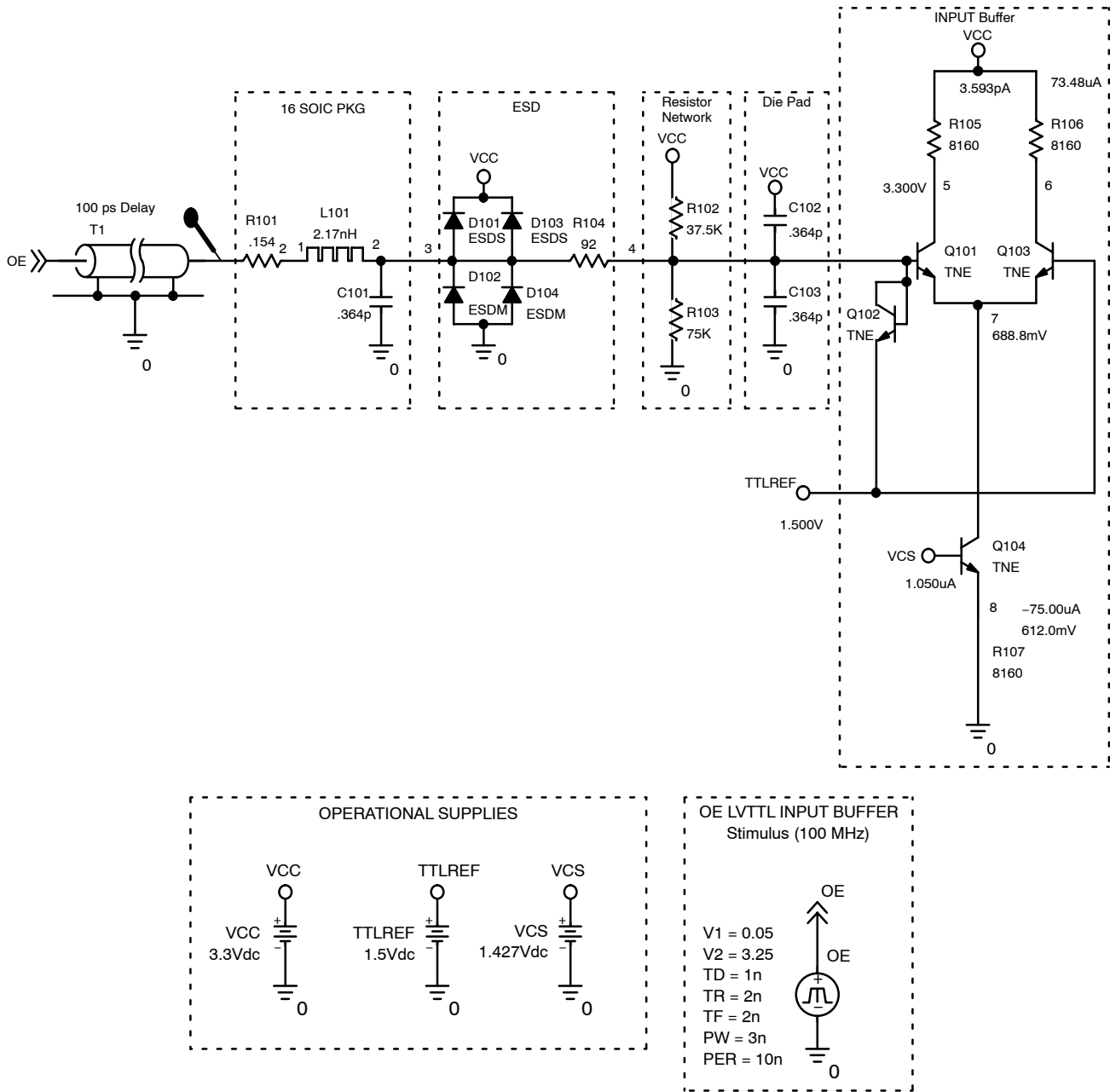


Figure 5. INBUF04 Input Buffer

NETLIST for INBUF04

```
V_OE      OE 0 PULSE 0.05 3.25 1n 2n 2n 3n 10n
V_TTLREF  $G_TTLREF 0 1.5Vdc
V_VCC     $G_VCC 0 3.3Vdc
V_VCS     $G_VCS 0 1.427Vdc
```

SUBCKT INBUF04

```
C_C101    0 3  .364p
C_C102    4 $G_VCC  .364p
C_C103    0 4  .364p
D_D101    3 $G_VCC ESDS
D_D102    0 3  ESDM
```

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```
D_D103 3 $G_VCC ESDM
D_D104 0 3 ESDS
L_L101 2 3 2.17nH
Q_Q101 5 4 7 TNE
Q_Q102 4 4 $G_TTLREF TNE
Q_Q103 6 $G_TTLREF 7 TNE
Q_Q104 7 $G_VCS 8 TNE
R_R101 1 2 .154
R_R102 4 $G_VCC 37.5K
R_R103 4 0 75K
R_R104 3 4 92
R_R105 5 $G_VCC 8160
R_R106 6 $G_VCC 8160
R_R107 0 8 8160
T_T1 OE 0 1 0 Z0=50 TD=100ps
END INBUF04
```

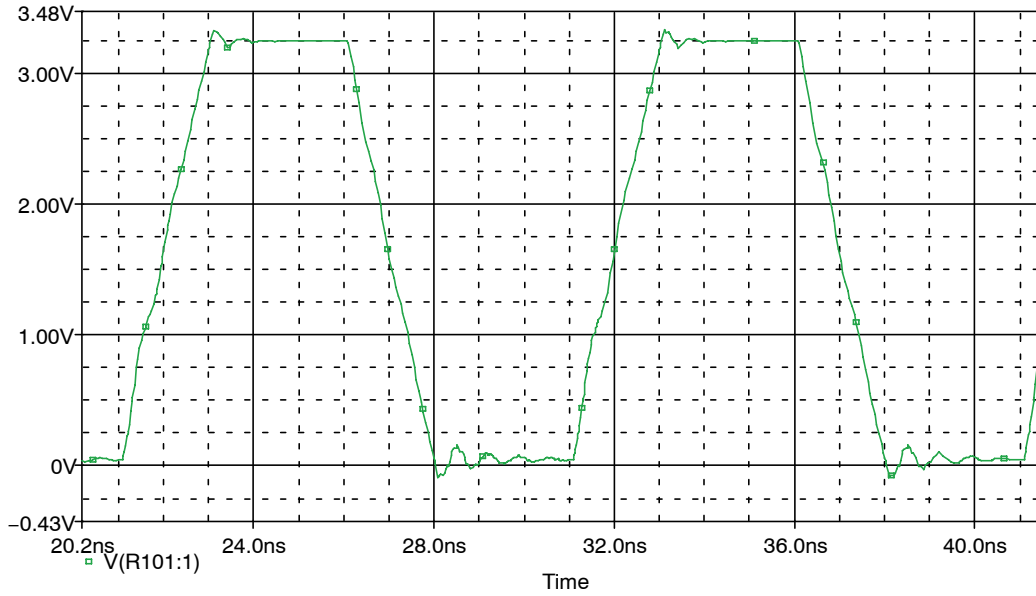


Figure 6. Typical LVCMOS Driving INBUF04 Input Buffer at 100 MHz

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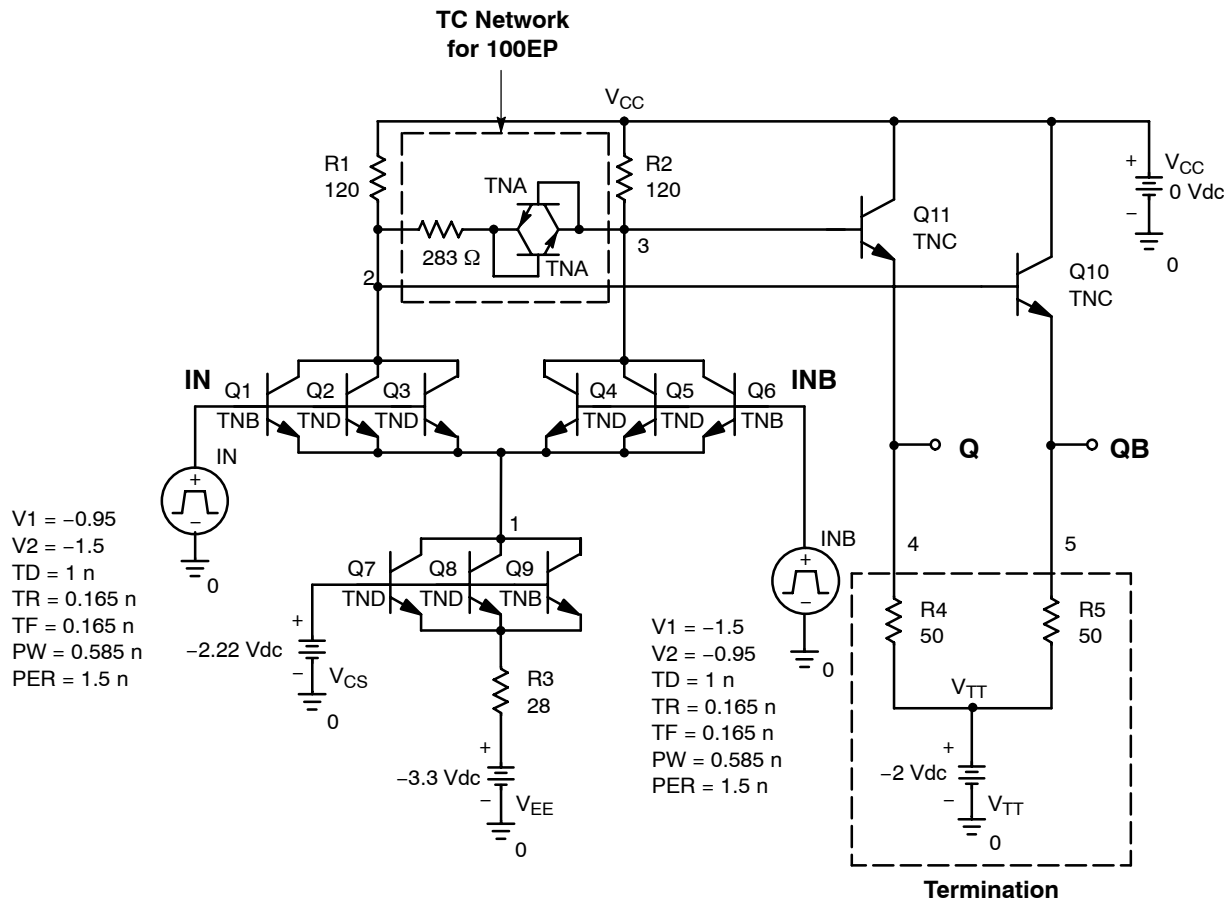


Figure 7. OBUF01

```
.SUBCKT OBUF01 IN INB VCS VCC VEE VTT
Q_Q1      2 IN 1 TNB
Q_Q2      2 IN 1 TND
Q_Q3      2 IN 1 TND
Q_Q4      3 INB 1 TND
Q_Q5      3 INB 1 TND
Q_Q6      3 INB 1 TNB
Q_Q7      1 VCS 10 TND
Q_Q8      1 VCS 10 TND
Q_Q9      1 VCS 10 TNB
Q_Q10     VCC 2 5 TNC
Q_Q11     VCC 3 4 TNC
R_R1      2 VCC 120
R_R2      3 VCC 120
R_R3      VEE 10 28
R_R4      VTT 4 50
R_R5      VTT 5 50
V_IN      IN 0
+PULSE -0.95 -1.5 1n 0.165n 0.165n 0.585n 1.5n
V_INB     INB 0
+PULSE -1.5 -0.95 1n 0.165n 0.165n 0.585n 1.5n
V_VCC     VCC 0 0Vdc
V_VEE     VEE 0 -3.3Vdc
V_VTT     VTT 0 -2Vdc
V_VCS     VCS 0 -2.22Vdc
.END OBUF01
```

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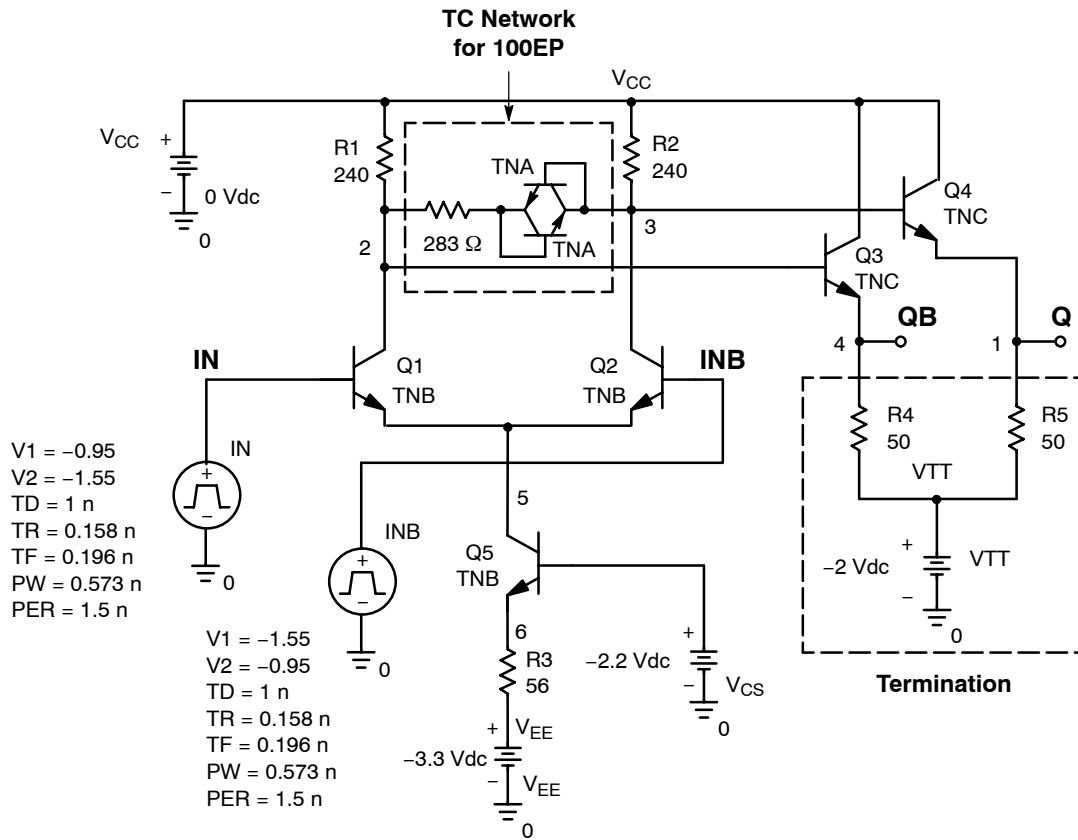


Figure 8. OBUF02

```
.SUBCKT OBUF02 IN INB VCC VCS VEE VTT
Q_Q1      2 IN 5 TNB
Q_Q2      3 INB 5 TNB
Q_Q3      VCC 2 4 TNC
Q_Q4      VCC 3 1 TNC
Q_Q5      5 VCS 6 TNB
R_R1      2 VCC 240
R_R2      3 VCC 240
R_R3      VEE 6 56
R_R4      VTT 4 50
R_R5      VTT 1 50
V_IN      IN 0
+PULSE   -0.95 -1.55 1n 0.158n 0.196n 0.573n 1.5n
V_INB     INB 0
+PULSE   -1.55 -0.95 1n 0.158n 0.196n 0.573n 1.5n
V_VCC     VCC 0 0Vdc
V_VEE     VEE 0 -3.3Vdc
V_VTT     VTT 0 -2Vdc
V_VCS     VCS 0 -2.2Vdc
.END OBUF02
```

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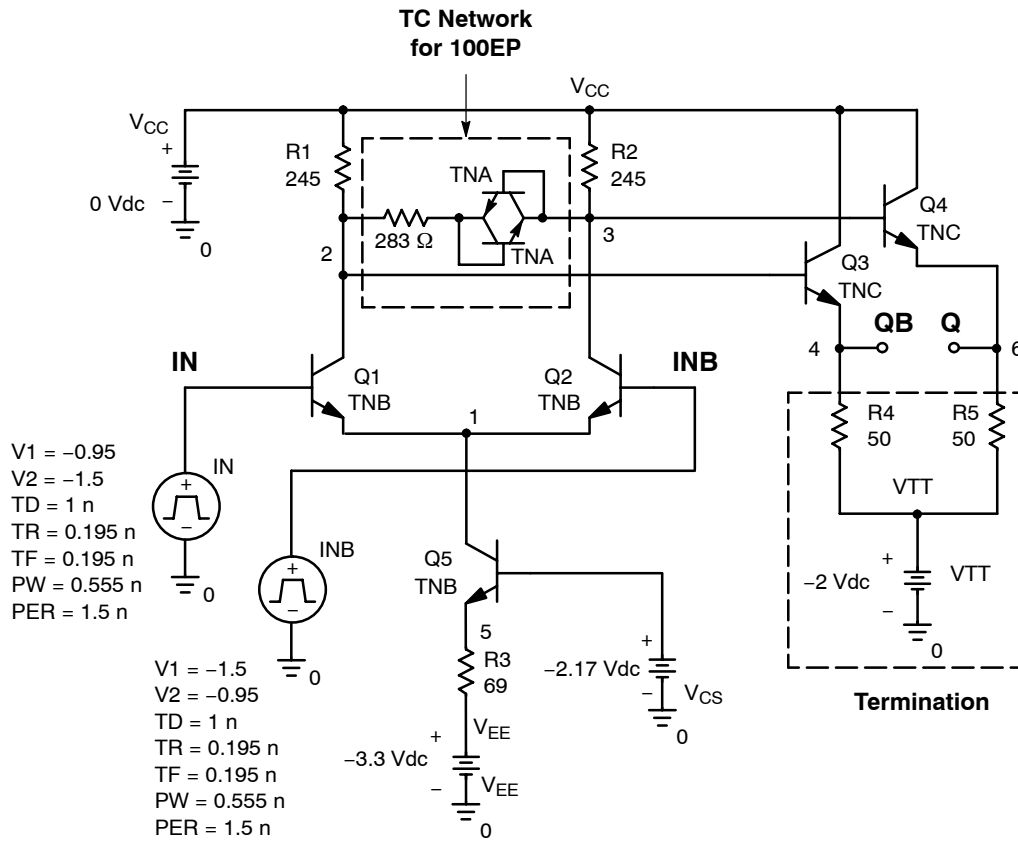
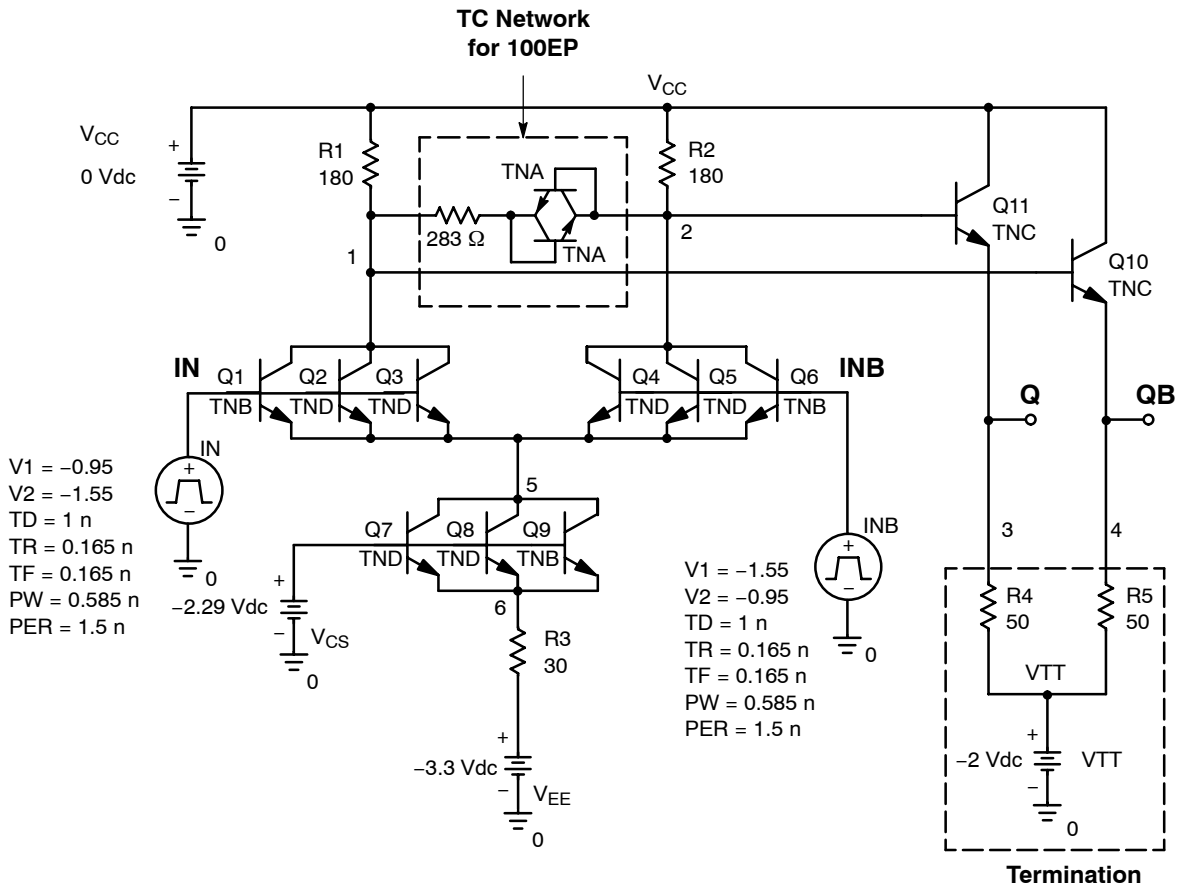


Figure 9. OBUF03

```
.SUBCKT OBUF03 IN INB VCC VCS VEE VTT
Q_Q1      2 IN 1 TNB
Q_Q2      3 INB 1 TNB
Q_Q3      VCC 2 4 TNC
Q_Q4      VCC 3 6 TNC
Q_Q5      1 VCS 5 TNB
R_R1      2 VCC 245
R_R2      3 VCC 245
R_R3      VEE 5 69
R_R4      VTT 4 50
R_R5      VTT 6 50
V_IN      IN 0
+PULSE -0.95 -1.5 1n 0.195n 0.195n 0.555n 1.5n
V_INB     INB 0
+PULSE -1.5 -0.95 1n 0.195n 0.195n 0.555n 1.5n
V_VCC     VCC 0 0Vdc
V_VEE     VEE 0 -3.3Vdc
V_VTT     VTT 0 -2Vdc
V_VCS     VCS 0 -2.17Vdc
.END OBUF03
```

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```

.SUBCKT OBUF04 IN INB VCS VCC VEE VTT
Q_Q1      1 IN 5 TNB
Q_Q2      1 IN 5 TND
Q_Q3      1 IN 5 TND
Q_Q4      2 INB 5 TND
Q_Q5      2 INB 5 TND
Q_Q6      2 INB 5 TNB
Q_Q7      5 VCS 6 TND
Q_Q8      5 VCS 6 TND
Q_Q9      5 VCS 6 TNB
Q_Q10     VCC 1 4 TNC
Q_Q11     VCC 2 3 TNC
R_R1      1 VCC 180
R_R2      2 VCC 180
R_R3      VEE 6 20
R_R4      VTT 3 50
R_R5      VTT 4 50
V_IN      IN 0
+PULSE -0.95 -1.55 1n 0.165n 0.165n 0.585n 1.5n
V_INB     INB 0
+PULSE -1.55 -0.95 1n 0.165n 0.165n 0.585n 1.5n
V_VCC     VCC 0 0Vdc
V_VEE     VEE 0 -3.3Vdc
V_VTT     VTT 0 -2Vdc
V_VCS     VCS 0 -2.29Vdc
.END OBUF04

```

AND8009/D

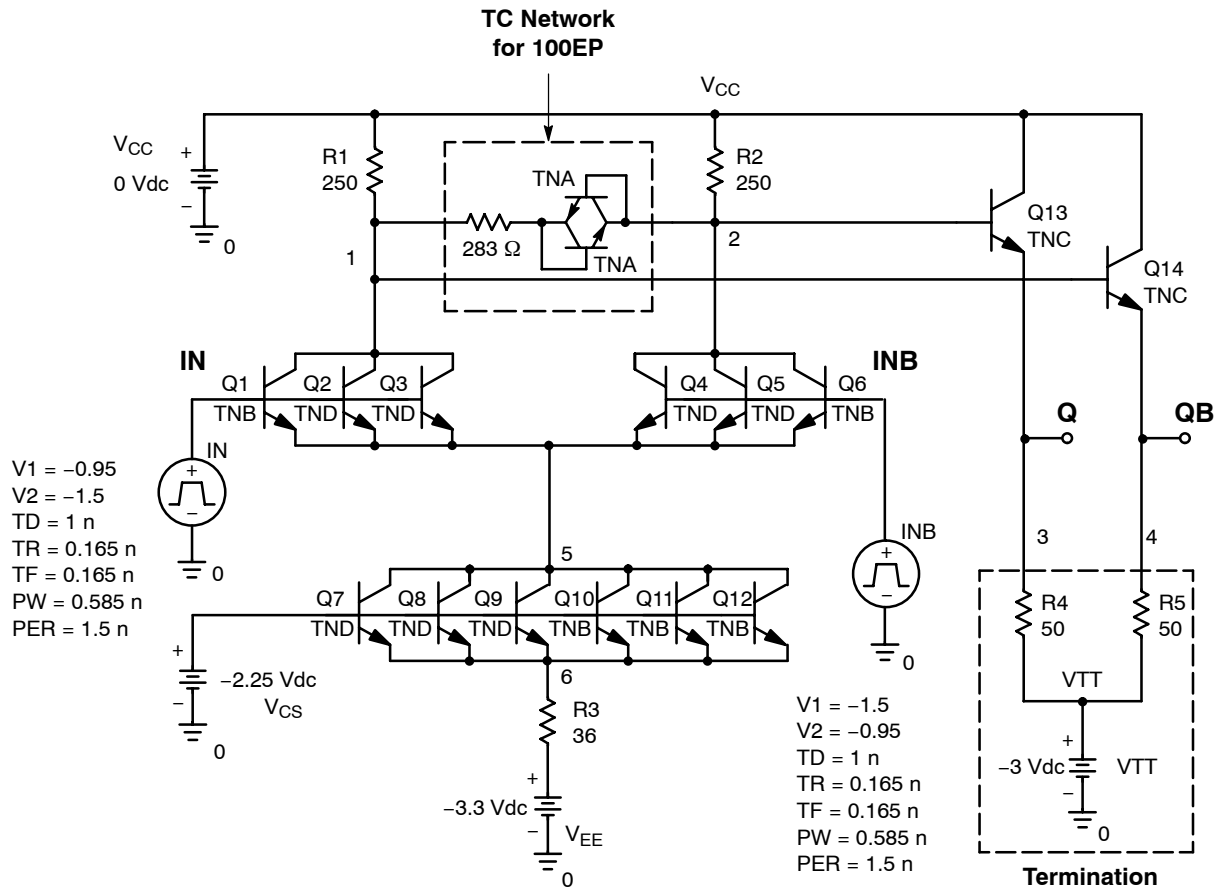


Figure 11. OBUF05

.SUBCKT OBUF05 IN INB VCS VCC VTT VEE

```

Q_Q1      1 IN 5 TNB
Q_Q2      1 IN 5 TND
Q_Q3      1 IN 5 TND
Q_Q4      2 INB 5 TND
Q_Q5      2 INB 5 TND
Q_Q6      2 INB 5 TNB
Q_Q7      5 VCS 6 TND
Q_Q8      5 VCS 6 TND
Q_Q9      5 VCS 6 TND
Q_Q10     5 VCS 6 TNB
Q_Q11     5 VCS 6 TNB
Q_Q12     5 VCS 6 TNB
Q_Q13     VCC 2 3 TNC
Q_Q14     VCC 1 4 TNC
R_R1      1 VCC 285
R_R2      2 VCC 285
R_R3      VEE 6 38
R_R4      VTT 3 50
R_R5      VTT 4 50
V_IN      IN 0 -1.33Vdc
+PULSE    -0.95 -1.5 1n 0.165n 0.165n 0.585n 1.5n
V_INB     INB 0
+PULSE    -1.5 -0.95 1n 0.165n 0.165n 0.585n 1.5n
V_VEE     VEE 0 -3.3Vdc
V_VCC     VCC 0 0Vdc
V_VTT     VTT 0 -3Vdc
V_VCS     VCS 0 -2.25Vdc
.END OBUF05

```


AND8009/D

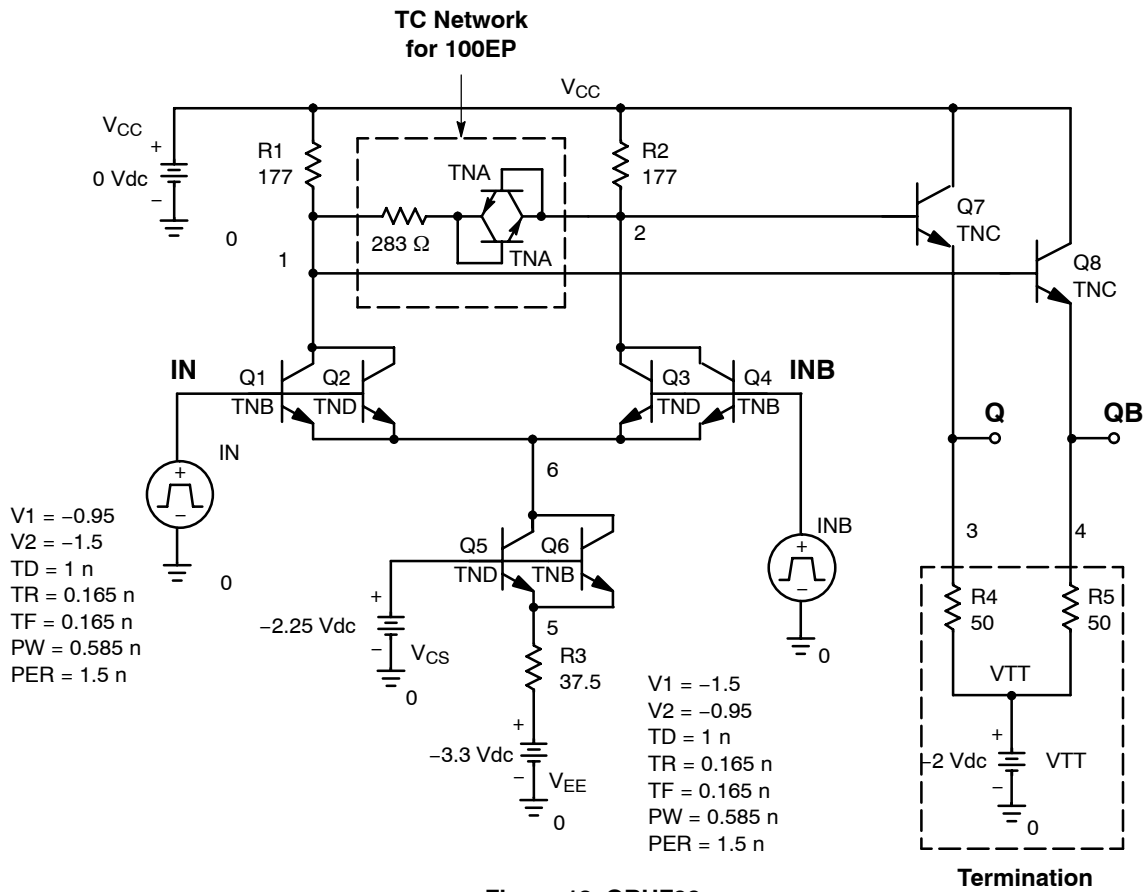


Figure 12. OBUF06

```
.SUBCKT OBUF06 IN INB VCC VCS VEE VTT
Q_Q1      1 IN 6 TNB
Q_Q2      1 IN 6 TND
Q_Q3      2 INB 6 TND
Q_Q4      2 INB 6 TNB
Q_Q5      6 VCS 5 TND
Q_Q6      6 VCS 5 TNB
Q_Q7      VCC 2 3 TNC
Q_Q8      VCC 1 4 TNC
R_R1      1 VCC 177
R_R2      2 VCC 177
R_R3      VEE 5 37.5
R_R4      VTT 3 50
R_R5      VTT 4 50
V_IN      IN 0
+PULSE -0.95 -1.5 1n 0.165n 0.165n 0.585n 1.5n
V_INB     INB 0
+PULSE -1.5 -0.95 1n 0.165n 0.165n 0.585n 1.5n
V_VEE     VEE 0 -3.3Vdc
V_VCC     VCC 0 0Vdc
V_VTT     VTT 0 -2Vdc
V_VCS     VCS 0 -2.25Vdc
.END OBUF06
```

AND8009/D

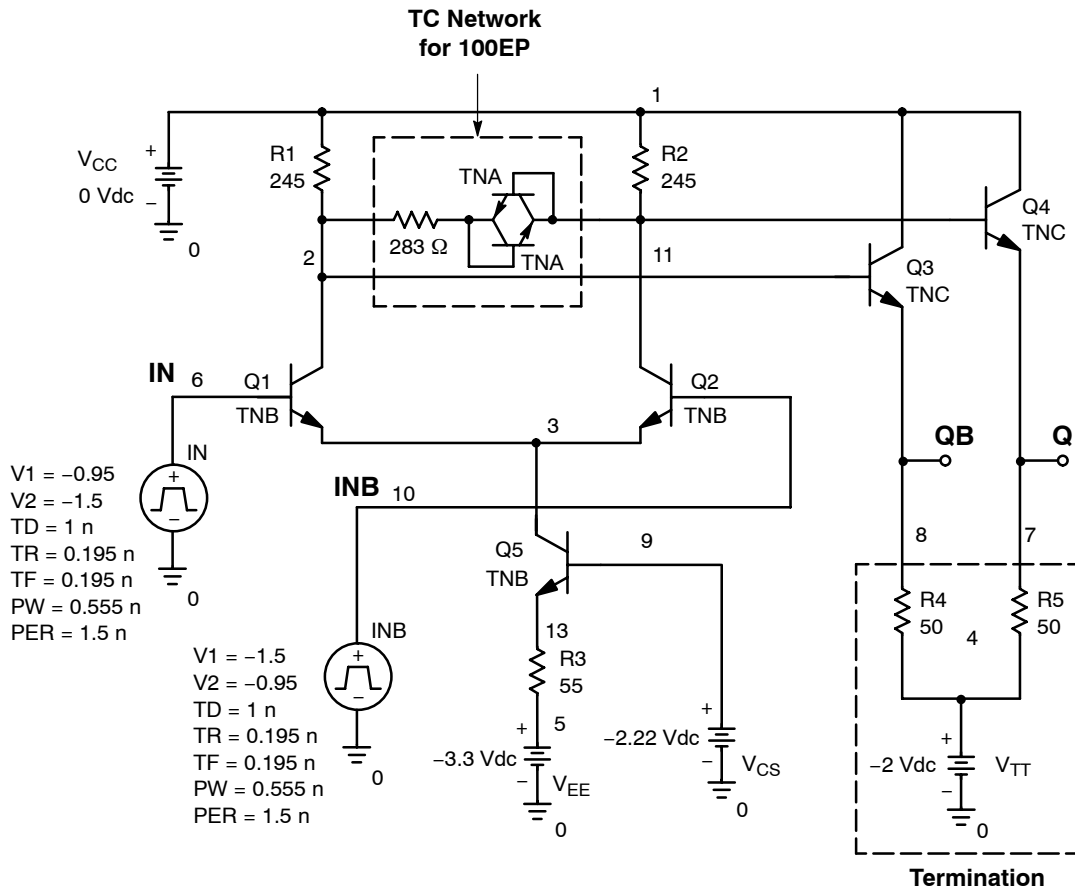


Figure 13. OBUF07

.SUBCKT OBUF07

```

Q_Q1      2 6 3 TNB
Q_Q2      11 10 3 TNB
Q_Q3      1 2 8 TNC
Q_Q4      1 11 7 TNC
Q_Q5      3 9 13 TNB
R_R1      2 1 245
R_R2      11 1 245
R_R3      5 13 55
R_R4      4 8 50
R_R5      4 7 50
V_IN      6 0
+PULSE -0.95 -1.5 1n 0.195n 0.195n 0.555n 1.5n
V_INB     10 0
+PULSE -1.5 -0.95 1n 0.195n 0.195n 0.555n 1.5n
V_VEE     5 0 -3.3Vdc
V_VCC     1 0 0Vdc
V_VTT     4 0 -2Vdc
V_VCS     9 0 -2.22Vdc
.END OBUF07
  
```

AND8009/D

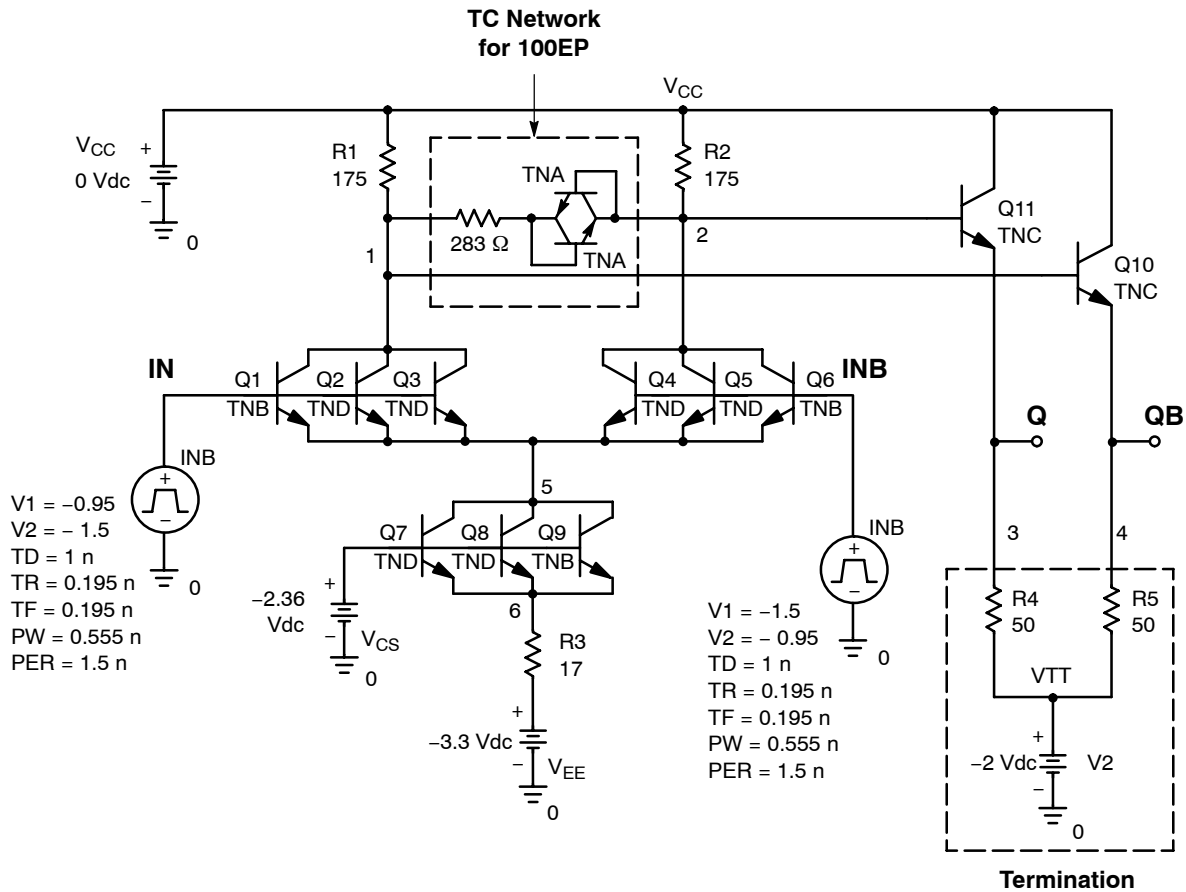


Figure 14. OBUF08

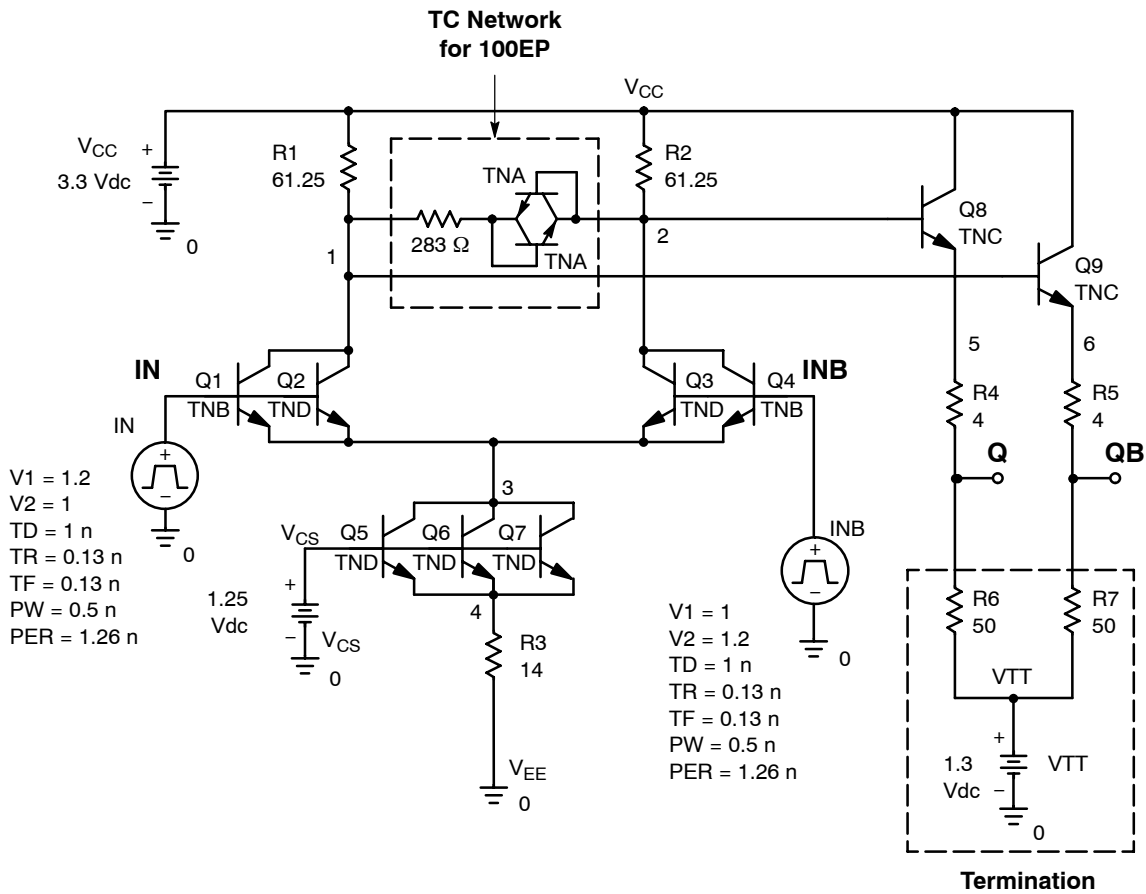
.SUBCKT OBUF08 IN INB VCC VCS VEE VTT

```

Q_Q1      1 IN 5 TNB
Q_Q2      1 IN 5 TND
Q_Q3      1 IN 5 TND
Q_Q4      2 INB 5 TND
Q_Q5      2 INB 5 TND
Q_Q6      2 INB 5 TNB
Q_Q7      5 VCS 6 TND
Q_Q8      5 VCS 6 TND
Q_Q9      5 VCS 6 TNB
Q_Q10     VCC 1 4 TNC
Q_Q11     VCC 2 3 TNC
R_R1      1 VCC 175
R_R2      2 VCC 175
R_R3      VEE 6 17
R_R4      VTT 3 50
R_R5      VTT 4 50
V_INB     INB 0
+PULSE    -1.5 -0.95 1n 0.195n 0.195n 0.555n 1.5n
V_IN      IN 0
+PULSE    -0.95 -1.5 1n 0.195n 0.195n 0.555n 1.5n
V_VEE     VEE 0 -3.3Vdc
V_VTT     VTT 0 -2Vdc
V_VCS     VCS 0 -2.36Vdc
V_VCC     VCC 0 0Vdc
.END OBUF08

```

AND8009/D



```

.SUBCKT OBUF09 IN INB VCC VCS VTT VEE Q QB
Q_Q1      1 IN 3 TNB
Q_Q2      1 IN 3 TND
Q_Q3      2 INB 3 TND
Q_Q4      2 INB 3 TNB
Q_Q5      3 VCS 4 TND
Q_Q6      3 VCS 4 TND
Q_Q7      3 VCS 4 TND
Q_Q8      VCC 2 5 TNC
Q_Q9      VCC 1 6 TNC
R_R1      1 VCC 61.25
R_R2      2 VCC 61.25
R_R3      VEE 4 14
R_R4      Q 5 4
R_R5      QB 6 4
R_R6      VTT Q 50
R_R7      VTT QB 50
V_INB     INB 0
+PULSE 1 1.2 1n 0.13n 0.13n 0.5n 1.26n
V_IN      IN 0
+PULSE 1.2 1 1n 0.13n 0.13n 0.5n 1.26n
V_VCS     VCS 0 1.25Vdc
V_VCC     VCC 0 3.3Vdc
V_VTT     VTT 0 1.3Vdc
.END OBUF09

```

AND8009/D

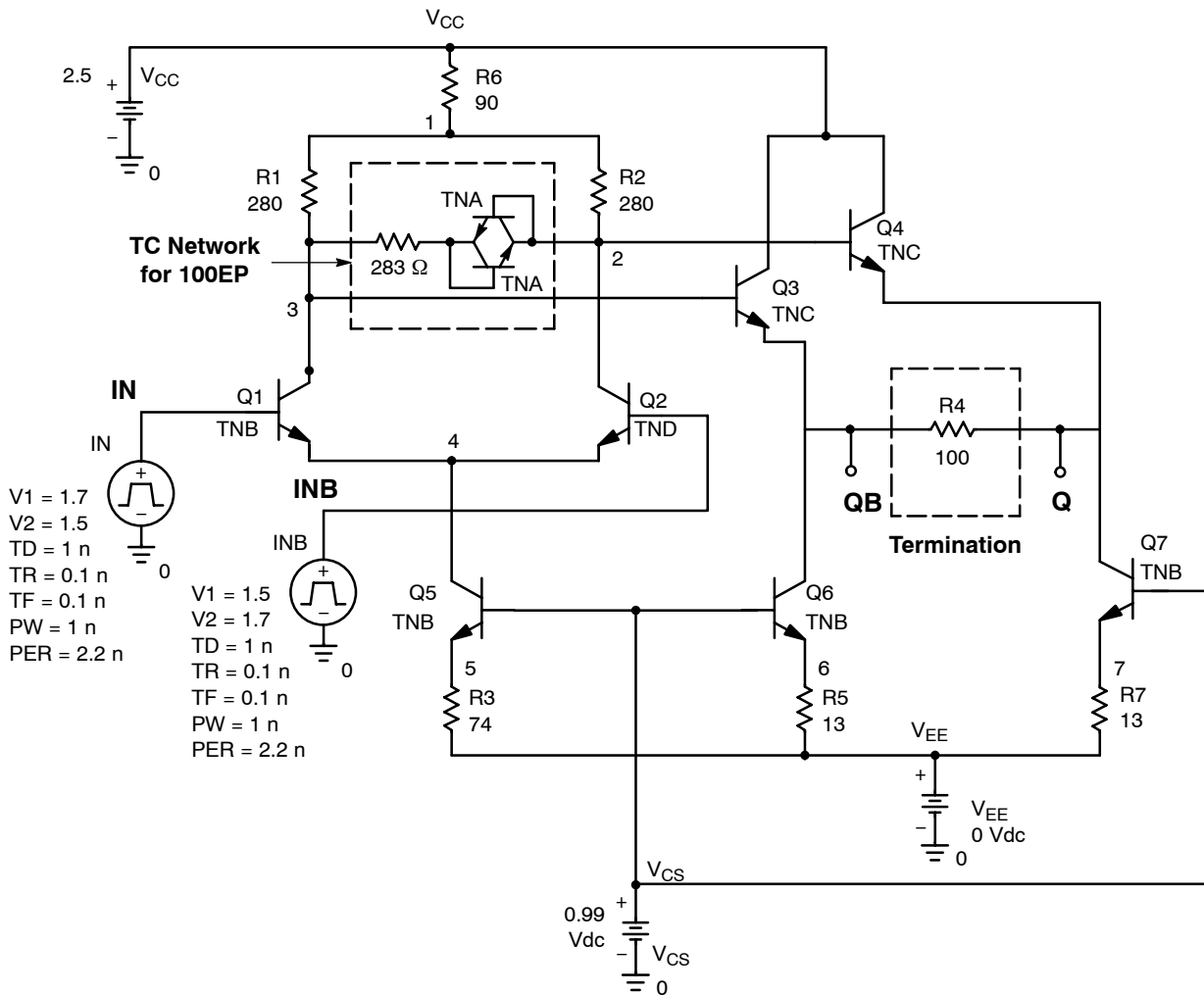


Figure 16. OBUF10

```

.SUBCKT OBUF10 IN INB VCC VCS VEE Q QB
Q_Q1      3 IN 4 TNB
Q_Q2      2 INB 4 TNB
Q_Q3      VCC 3 QB TNC
Q_Q4      VCC 2 Q TNC
Q_Q5      4 VCS 5 TNB
Q_Q6      QB VCS 6 TNB
Q_Q7      Q VCS 7 TNB
R_R1      3 1 295
R_R2      2 1 295
R_R3      VEE 5 64.3
R_R4      QB Q 100
R_R5      VEE 6 10
R_R6      1 VCC 61.25
R_R7      VEE 7 10
V_IN      IN 0
+PULSE 1.5 1.7 1n 0.1n 0.1n 1n 2.6n
V_INB     INB 0
+PULSE 1.7 1.5 1n 0.1n 0.1n 1n 2.6n
V_VCC     VCC 0 2.5
V_VEE     VEE 0 0Vdc
V_VCS     VCS 0 0.99Vdc
.END OBUF10
  
```

AND8009/D

V_{HSTL} Internal Constant Voltage Source

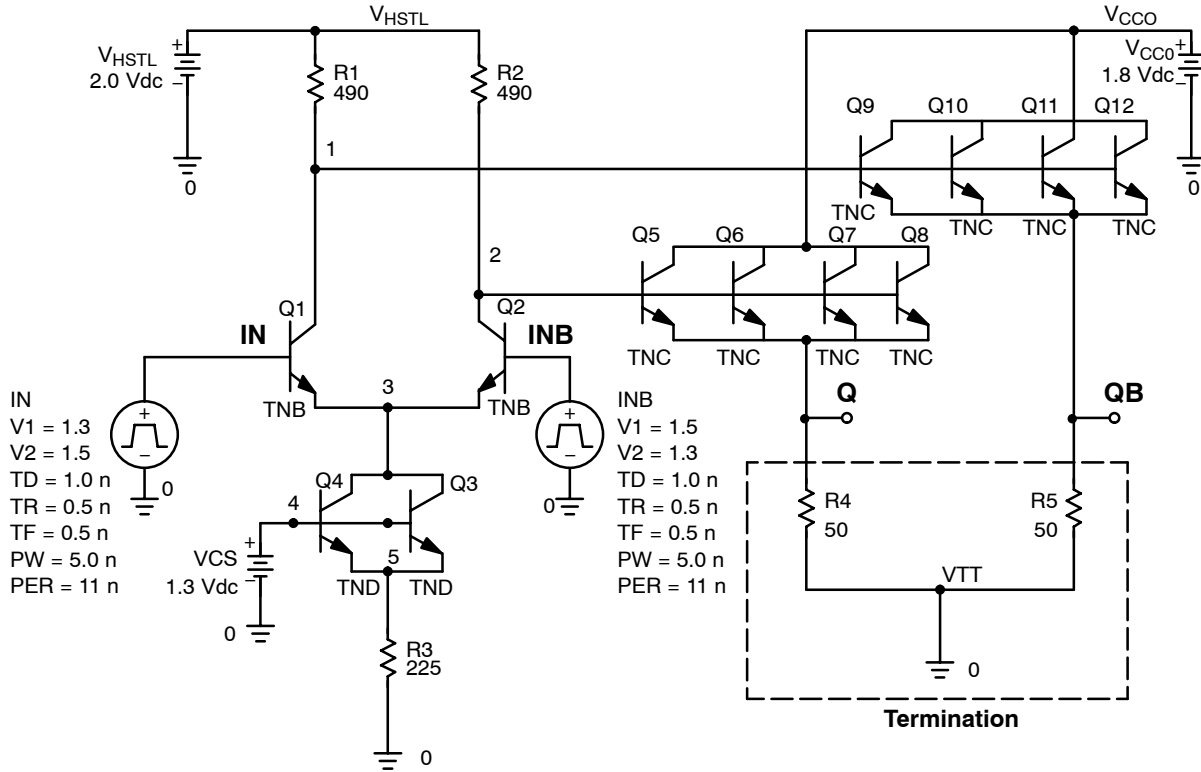


Figure 17. OBUF11

```
.SUBCKT OBUF11 IN INB VCCO VHSTL Q QB
Q_Q1      1 IN 3 TNB
Q_Q2      2 INB 3 TNB
Q_Q3      3 4 5 TND
Q_Q4      3 4 5 TND
Q_Q5      VCCO 2 Q TNC
Q_Q6      VCCO 2 Q TNC
Q_Q7      VCCO 2 Q TNC
Q_Q8      VCCO 2 Q TNC
Q_Q9      VCCO 1 QB TNC
Q_Q10     VCCO 1 QB TNC
Q_Q11     VCCO 1 QB TNC
Q_Q12     VCCO 1 QB TNC
R_R1      1 VHSTL 490
R_R2      2 VHSTL 490
R_R3      0 5 225
R_R4      0 Q 50
R_R5      0 QB 50
V_IN      IN 0
+PULSE 1.3 1.5 1n 0.5n 0.5n 5n 11n
V_INB     INB 0
+PULSE 1.5 1.3 1n 0.5n 0.5n 5n 11n
V_VCCO    VCCO 0 1.8Vdc
V_VHSTL   VHSTL 0 2.0Vdc
V_VCS     4 0 1.3Vdc
.END OBUF11
```

AND8009/D

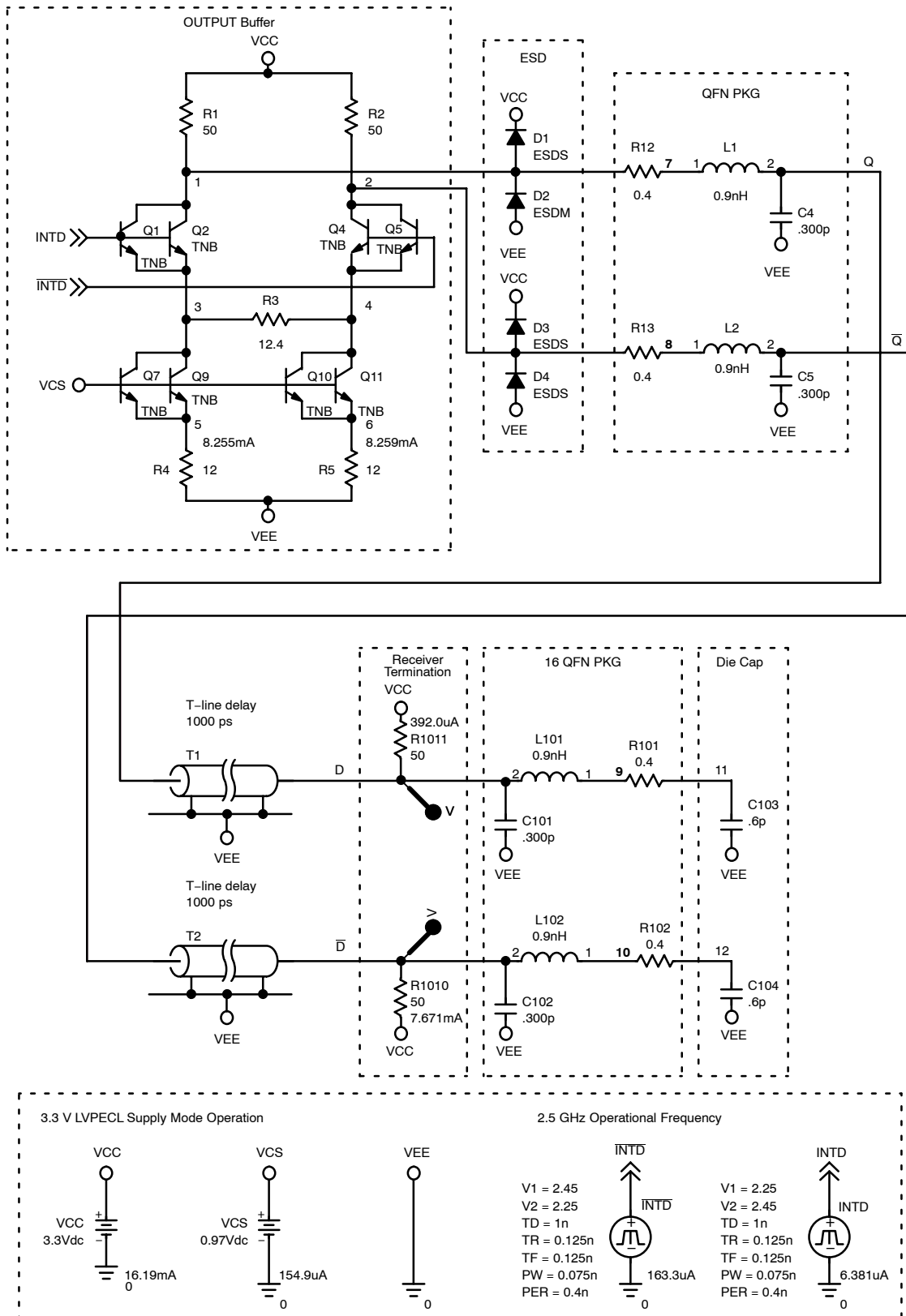


Figure 18. OBUF12 Driving Typical Receiver with Termination and 1000 ps T-Line Delay

AND8009/D

Netlist for OBUF12 Driving Typical Receiver with Termination and 1000 ps T-line delay

```
V_VCC $G_VCC 0 3.3Vdc
V_VCS $G_VCS 0 0.97Vdc
V_INTD INTD 0 +PULSE 2.25 2.45 1n 0.125n 0.125n 0.075n 0.4n
V_INTDb INTDb 0 +PULSE 2.45 2.25 1n 0.125n 0.125n 0.075n 0.4n
```

.SUBCKT OBUF12 VCC VCS VEE INT INTb Q Qb

```
Q_Q1 1 INTD 3 TNB
Q_Q10 4 $G_VCS 6 TNB
Q_Q11 4 $G_VCS 6 TNB
Q_Q2 1 INTD 3 TNB
Q_Q4 2 INTDb 4 TNB
Q_Q5 2 INTDb 4 TNB
Q_Q7 3 $G_VCS 5 TNB
Q_Q9 3 $G_VCS 5 TNB
D_D1 1 $G_VCC ESDS
D_D2 0 1 ESDM
D_D3 2 $G_VCC ESDS
D_D4 0 2 ESDS
C_C4 0 Q .300p
C_C5 0 Qb .300p
R_R1 1 $G_VCC 50
R_R2 2 $G_VCC 50
R_R3 4 3 12.4
R_R4 0 5 12
R_R5 0 6 12
L_L1 7 Q 0.9nH
L_L2 8 Qb 0.9nH
```

.END OBUF12

.SUBCKT RECEIVER VCC VEE D Db

```
T_T1 Q 0 D 0 Z0=50 TD=1000ps
T_T2 Qb 0 Db 0 Z0=50 TD=1000ps
C_C101 0 D .300p
C_C102 0 Db .300p
C_C103 0 11 .6p
C_C104 0 12 .6p
L_L101 9 D 0.9nH
L_L102 10 Db 0.9nH
R_R101 11 9 0.4
R_R1010 Db $G_VCC 50
R_R1011 D $G_VCC 50
R_R102 12 10 0.4
R_R12 1 7 0.4
R_R13 2 8 0.4
```

.END RECEIVER

AND8009/D

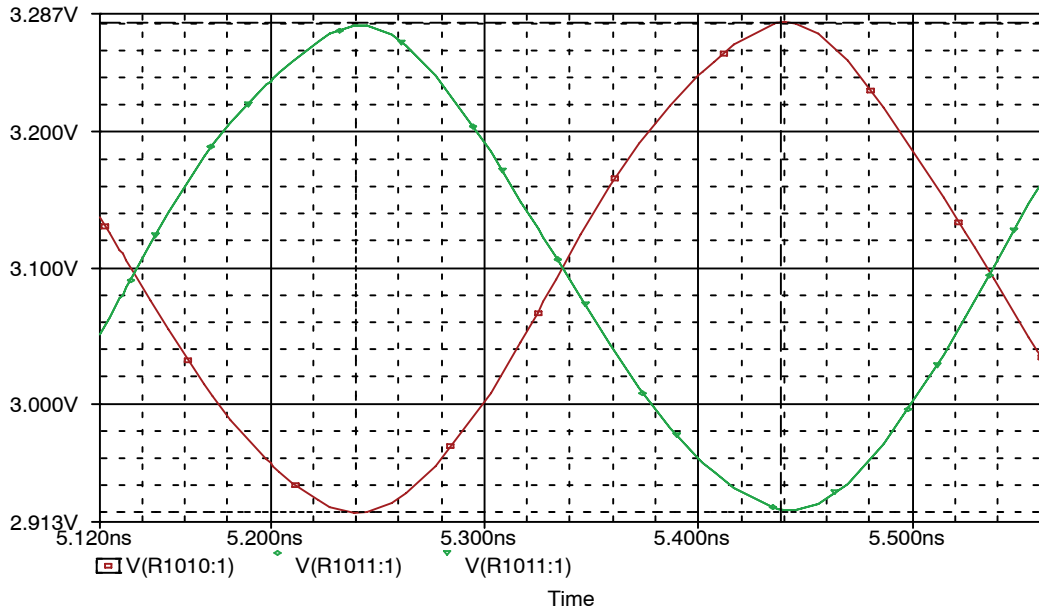


Figure 19. OBUF12 at 2.5 GHz Operation Frequency; V_{OUTamp} at 360 mV_{pp}; V_{OH} at 3.28 V; V_{OL} at 2.92 V; t_r/t_f (20% – 80%) is 86 ps (With Receiver Load)

AND8009/D

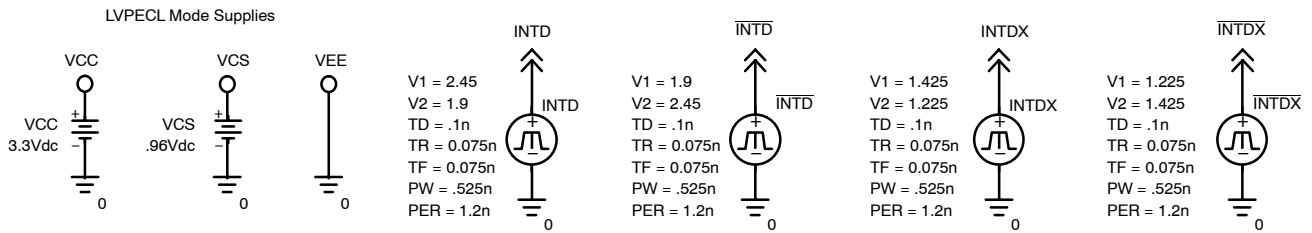
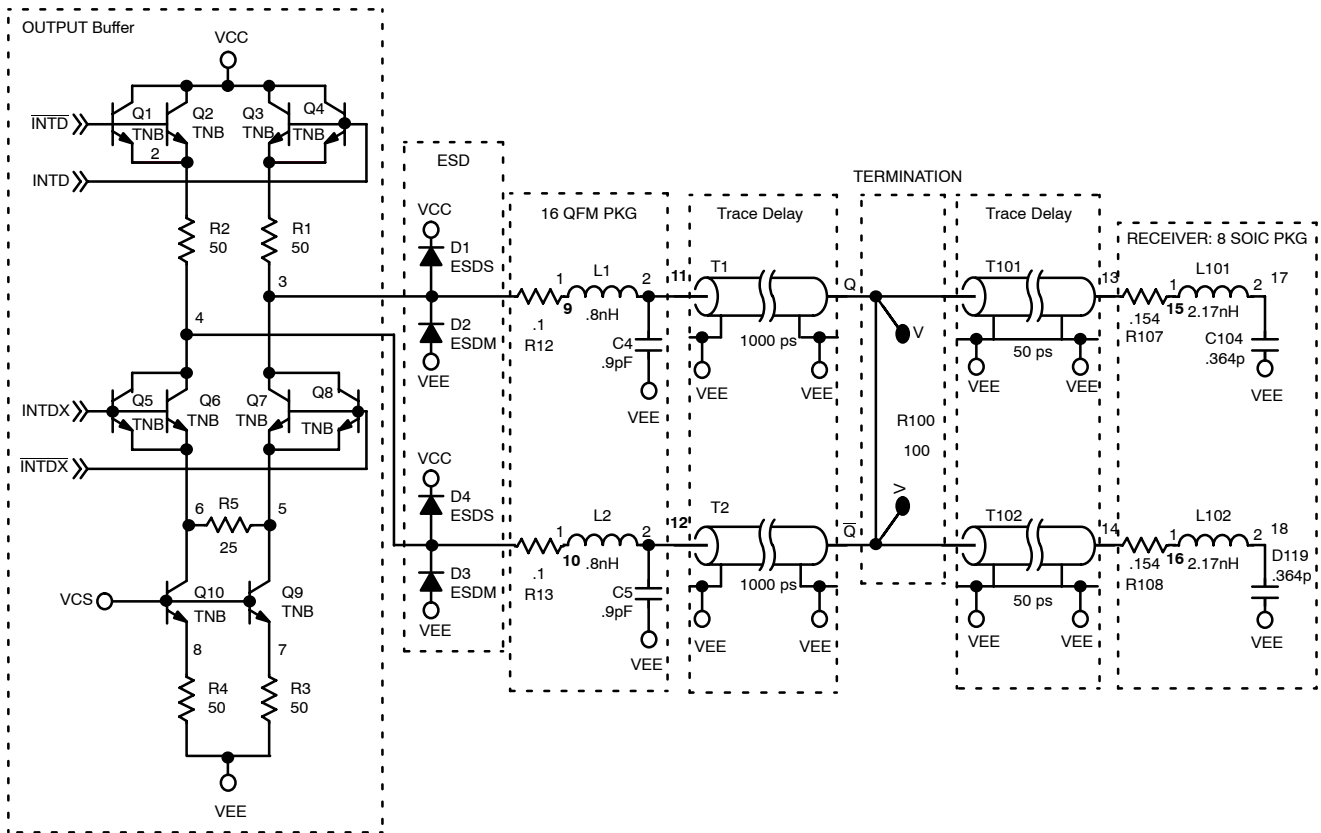


Figure 20. OBUF13 With Termination And Receiver Package Load

SPICE NETLIST for OBUF13:

```

V_VCC      $G_VCC 0 3.3Vdc
V_VCS      $G_VCS 0 .96Vdc
V_INTD     INTD 0 PULSE 2.45 1.9 .1n 0.075n 0.075n .525n 1.2n
V_INTDb    INTDB 0 PULSE 1.9 2.45 .1n 0.075n 0.075n .525n 1.2n
V_INTDX    INTDX 0 PULSE 1.225 1.425 .1n 0.075n 0.075n .525n 1.2n
V_INTDXb   INTDXB 0 PULSE 1.425 1.225 .1n 0.075n 0.075n .525n 1.2n

.SUBCKT OBUF13
C_C104     0 13 .364p
C_C4       0 11 .9pF
C_C5       0 12 .9pF
C_D119     0 14 .364p
D_D1       3 $G_VCC ESDS
D_D2       0 3 ESDM
D_D3       0 4 ESDM
    
```

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```

D_D4      4 $G_VCC ESDS
L_L1      9 11  .8nH
L_L101    11 13  2.17nH
L_L102    12 14  2.17nH
L_L2      10 12  .8nH
Q_Q1      $G_VCC INTDB 2 TNB
Q_Q10     6 $G_VCS 8 TNB
Q_Q2      $G_VCC INTDB 2 TNB
Q_Q3      $G_VCC INTD 1 TNB
Q_Q4      $G_VCC INTD 1 TNB
Q_Q5      4 INTDX 6 TNB
Q_Q6      4 INTDX 6 TNB
Q_Q7      3 INTDXB 5 TNB
Q_Q8      3 INTDXB 5 TNB
Q_Q9      5 $G_VCS 7 TNB
R_R1      3 1  50
R_R100    Q QB 100
R_R107    9 11  .154
R_R108    10 12 .154
R_R12     3 9  .1
R_R13     4 10 .1
R_R2      4 2  50
R_R3      0 7  50
R_R4      0 8  50
R_R5      5 6  25
T_T1      11 0 Q 0 Z0=50 TD=1000ps
T_T101    Q 0 9 0 Z0=50 TD=50ps
T_T102    QB 0 10 0 Z0=50 TD=50ps
T_T2      12 0 QB 0 Z0=50 TD=1000ps
.END OBUF13

```

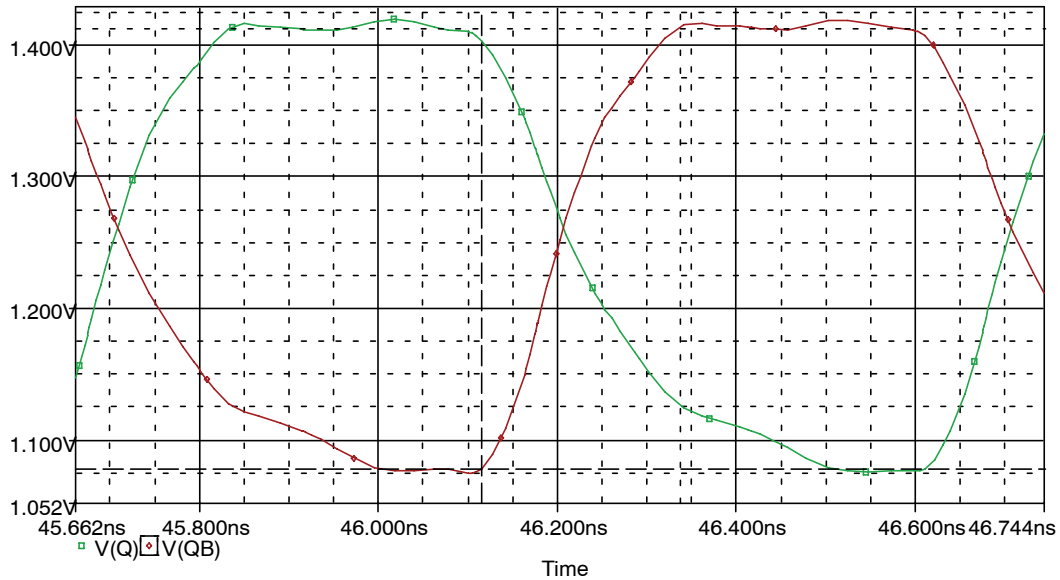


Figure 21. OBUF13 Typical Waveform at 1.0 GHz with Termination and Receiver Package Load (95ps t_r/t_f)

AND8009/D

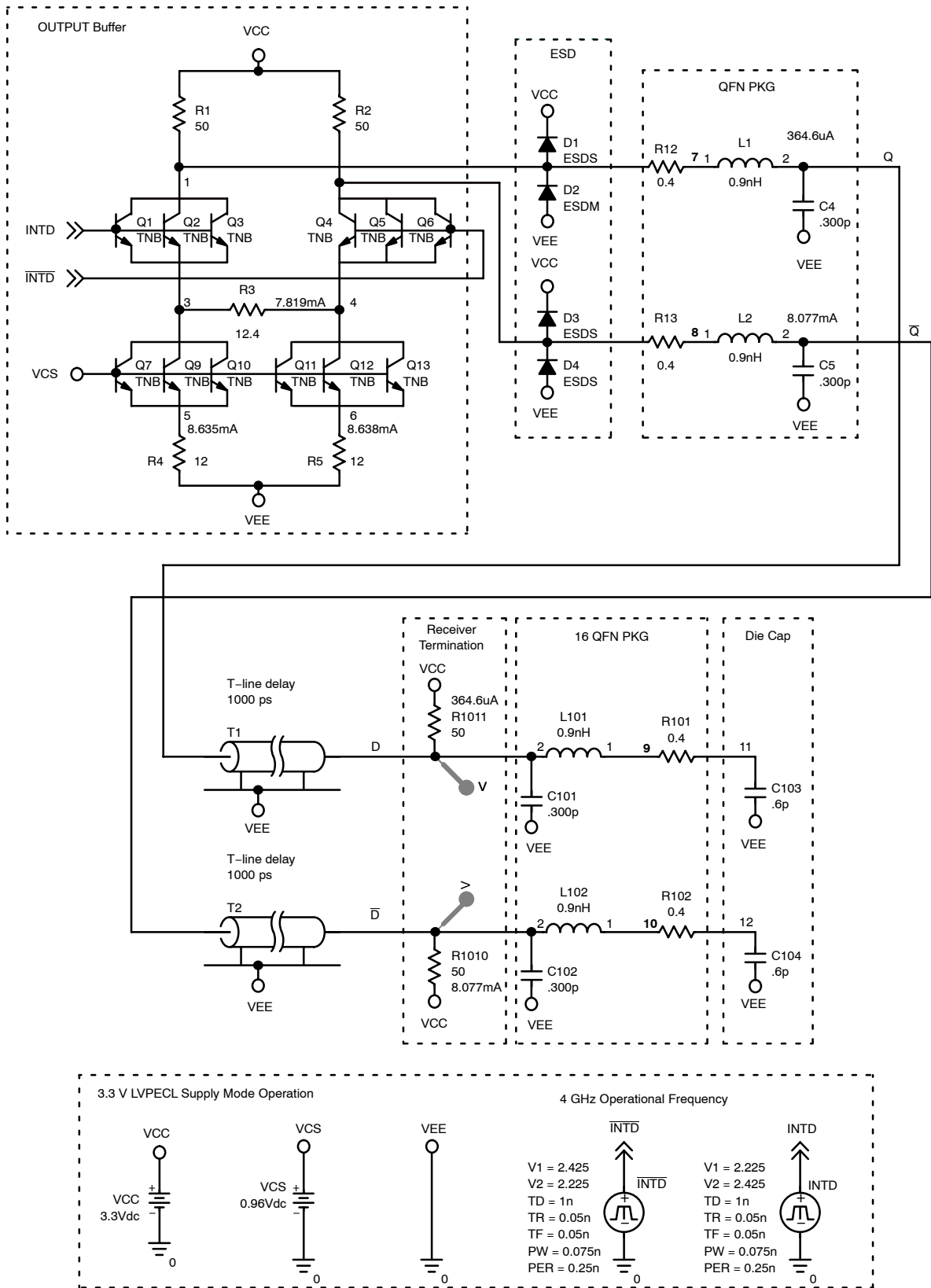


Figure 22. OBUF14 With Termination And Reciever Package Load

AND8009/D

NETLIST for OBUF14

```
V_INTD      INTD 0  +PULSE 2.225 2.425 1n 0.05n 0.05n 0.075n 0.25n
V_INTDb     INTDB 0 +PULSE 2.425 2.225 1n 0.05n 0.05n 0.075n 0.25n
V_VCC       $G_VCC 0 3.3Vdc
V_VCS       $G_VCS 0 0.96Vdc
```

.SUBCKT OBUF14 VCC VCS INTD INTDb Q Qb

```
Q_Q1        1 INTD 3 TNB
Q_Q2        1 INTD 3 TNB
Q_Q3        1 INTD 3 TNB
Q_Q4        2 INTDB 4 TNB
Q_Q5        2 INTDB 4 TNB
Q_Q6        2 INTDB 4 TNB
Q_Q7        3 $G_VCS 5 TNB
Q_Q9        3 $G_VCS 5 TNB
Q_Q10       3 $G_VCS 5 TNB
Q_Q11       4 $G_VCS 6 TNB
Q_Q12       4 $G_VCS 6 TNB
Q_Q13       4 $G_VCS 6 TNB
R_R1        1 $G_VCC 50
R_R2        2 $G_VCC 50
R_R3        4 3 12.4
R_R4        0 5 12
R_R5        0 6 12
R_R12       1 7 0.4
R_R13       2 8 0.4
D_D1        1 $G_VCC ESDS
D_D2        0 1 ESDM
D_D3        2 $G_VCC ESDS
D_D4        0 2 ESDS
C_C4        0 Q .300p
C_C5        0 QB .300p
L_L1        7 Q 0.9nH
L_L2        8 QB 0.9nH
```

.END OBUF14

.SUBCKT RECEIVER VCC VCS D Db

```
T_T1        Q 0 D 0 Z0=50 TD=1000ps
T_T2        QB 0 DB 0 Z0=50 TD=1000ps
C_C101      0 D .300p
C_C102      0 DB .300p
C_C103      0 11 .6p
C_C104      0 12 .6p
L_L101      9 D 0.9nH
L_L102      10 DB 0.9nH
R_R101      11 9 0.4
R_R102      12 10 0.4
R_R1010     DB $G_VCC 50
R_R1011     D $G_VCC 50
```

.END RECEIVER

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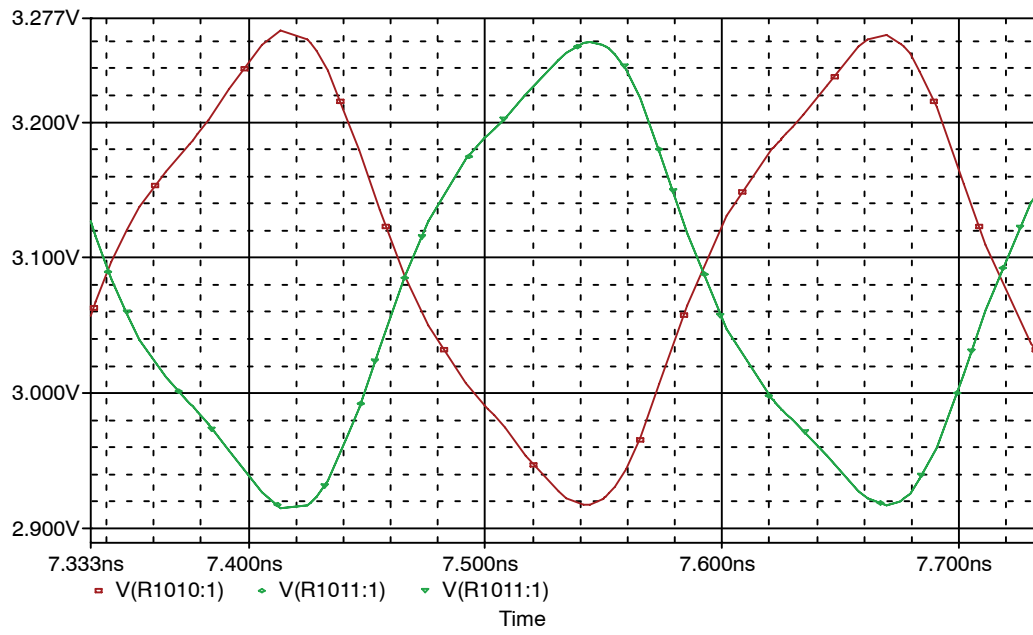


Figure 23. OBUF14 Typical Output Waveform at 4 GHz Operation; Amplitude 345 mV_{pp}; V_{OL} 2.91, V_{OH} 3.26 t_r/t_f 60 ps

AND8009/D

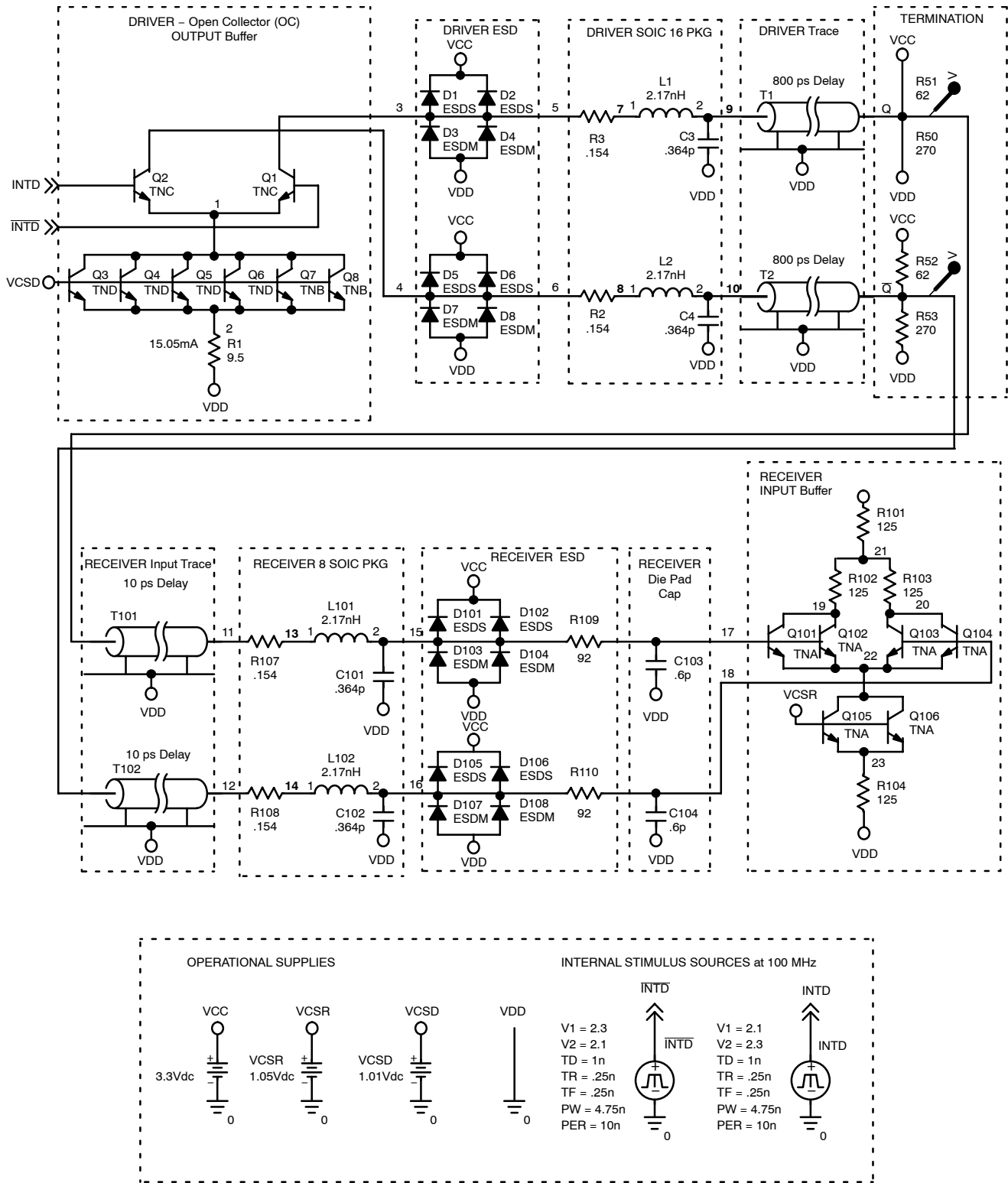


Figure 24. An OBUF15 Open Collector Output Buffer Driving A Typical LVPECL Receiver

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NETLIST for OBUF15

V_INTD INTD 0 PULSE 2.1 2.3 1n .25n .25n 4.75n 10n
V_INTDb INTDB 0 PULSE 2.3 2.1 1n .25n .25n 4.75n 10n
V_VCC \$G_VCC 0 3.3Vdc
V_VCSD \$G_VCSD 0 1.01Vdc
V_VCSR \$G_VCSR 0 1.05Vdc

SUBCKT OBUF15

Q_Q1 3 INTDB 1 TNC
Q_Q2 4 INTD 1 TNC
Q_Q3 1 \$G_VCSD 2 TND
Q_Q4 1 \$G_VCSD 2 TND
Q_Q5 1 \$G_VCSD 2 TND
Q_Q6 1 \$G_VCSD 2 TND
Q_Q7 1 \$G_VCSD 2 TNB
Q_Q8 1 \$G_VCSD 2 TNB
R_R1 0 2 9.5
D_D1 3 \$G_VCC ESDS
D_D2 3 \$G_VCC ESDS
D_D3 0 3 ESDM
D_D4 0 3 ESDM
D_D5 4 \$G_VCC ESDS
D_D6 4 \$G_VCC ESDS
D_D7 0 4 ESDM
D_D8 0 4 ESDM
R_R2 4 8 .154
R_R3 3 7 .154
L_L1 7 9 2.17nH
L_L2 8 10 2.17nH
C_C3 0 9 .364p
C_C4 0 10 .364p
T_T1 9 0 Q 0 Z0=50 TD=800ps
T_T2 10 0 QB 0 Z0=50 TD=800ps
R_R50 Q 0 270
R_R51 Q \$G_VCC 62
R_R52 QB \$G_VCC 62
R_R53 0 QB 270
.END

SUBCKT RECEIVER

C_C101 0 15 .364p
C_C102 0 16 .364p
C_C103 0 17 .6p
C_C104 0 18 .6p
D_D101 15 \$G_VCC ESDS
D_D102 15 \$G_VCC ESDS
D_D103 0 15 ESDM
D_D104 0 15 ESDM
D_D105 16 \$G_VCC ESDS
D_D106 16 \$G_VCC ESDS
D_D107 0 16 ESDM
D_D108 0 16 ESDM
L_L101 13 15 2.17nH
L_L102 14 16 2.17nH
Q_Q101 19 17 22 TNA
Q_Q102 19 17 22 TNA
Q_Q103 20 18 22 TNA
Q_Q104 20 18 22 TND
Q_Q105 22 \$G_VCSR 23 TNA
Q_Q106 22 \$G_VCSR 23 TNA
R_R101 21 \$G_VCC 125
R_R102 19 21 125
R_R103 20 21 125

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```
R_R104      0 23 125
R_R107      11 13 .154
R_R108      12 14 .154
R_R109      15 17 92
R_R110      16 18 92
T_T101      Q 0 11 0 Z0=50 TD=10ps
T_T102      QB 0 12 0 Z0=50 TD=10ps
.END RECEIVER
```

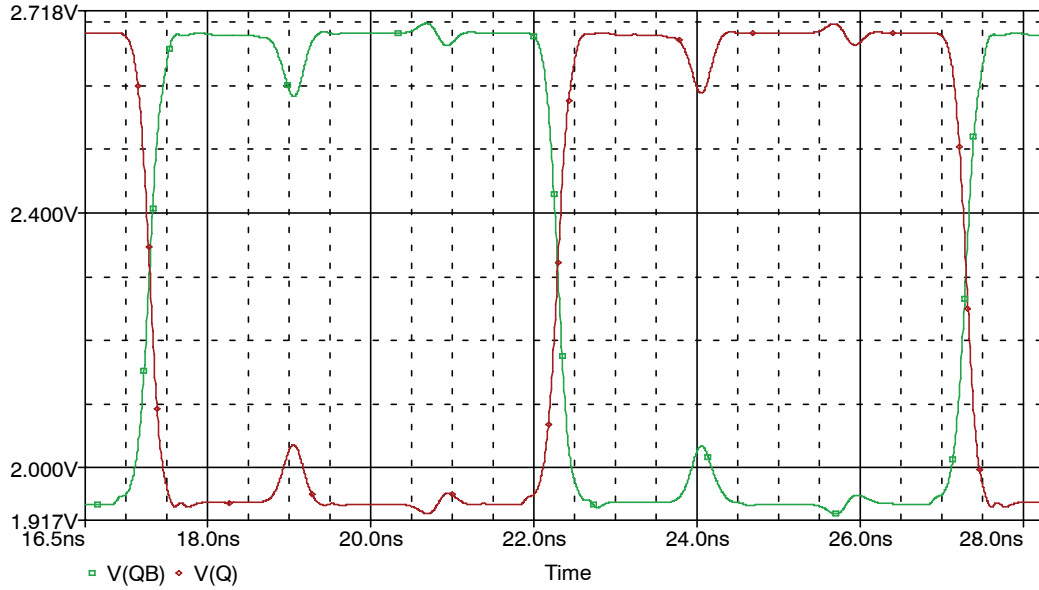
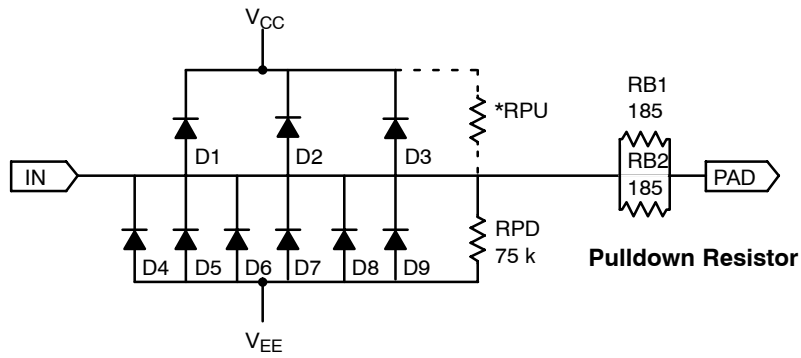


Figure 25. OBUF15 Output Driving LVPECL Receiver Typical Waveforms at 100 MHz; V_{OH} 1.94 V; V_{OL} 2.68 V; V_{amp} 736 mV; 199 ps t_r/t_f at 2.09 V and 2.53 V (20%/80%)

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* See device data sheet

Figure 26. Input ESD

```
.SUBCKT IN_ESD VCC VEE IN PAD
D1      IN      VCC      ESDM
D2      IN      VCC      ESDM
D3      IN      VCC      ESDM
D4      VEE     IN       ESDM
D5      VEE     IN       ESDS
D6      VEE     IN       ESDM
D7      VEE     IN       ESDS
D8      VEE     IN       ESDM
D9      VEE     IN       ESDS
RPD     IN      VEE     75K
RPU     IN      VCC     36.5K
RB1     IN      PAD     185
RB2     IN      PAD     185
.ENDS IN_ESD
```

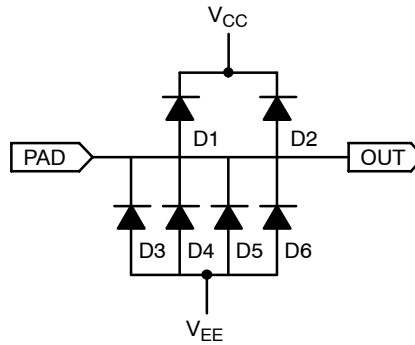


Figure 27. Output ESD

```
.SUBCKT OUT_ESD VCC VEE OUT
D1      OUT     VCC     ESDM
D2      OUT     VCC     ESDM
D3      VEE     OUT     ESDM
D4      VEE     OUT     ESDS
D5      VEE     OUT     ESDM
D6      VEE     OUT     ESDS
.ENDS OUT_ESD
```

AND8009/D

The following is an example of a typical run-deck file which might be used to simulate Figure 28 to produce output waveform shown in Figure 29.

TYPICAL TEST CIRCUIT

```

VCC      VCC      0      0V
VEE      VEE      0      -3.3V
VCS      VCS      0      -2.2V
VTT      VTT      0      -2.0V
VIN      IN       0      PULSE(-1.7 -0.95 5NS 5NS 5NS 50NS 110NS)
VINB     INB      0      PULSE(-0.95 -1.7 5NS 5NS 5NS 50NS 110NS)
.GROUND  0
.TRAN    0.2NS    120NS
    
```

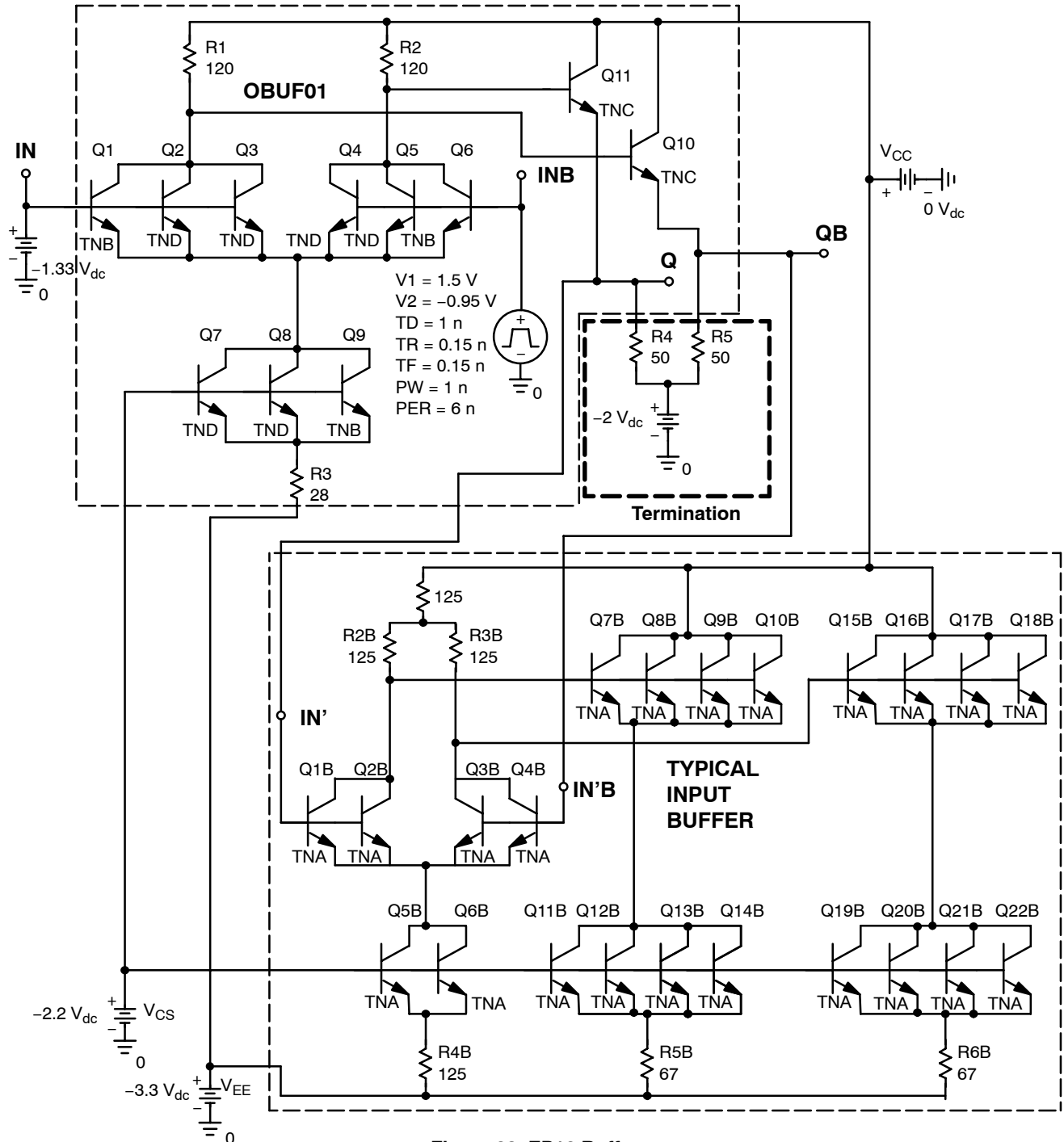


Figure 28. EP16 Buffer

AND8009/D

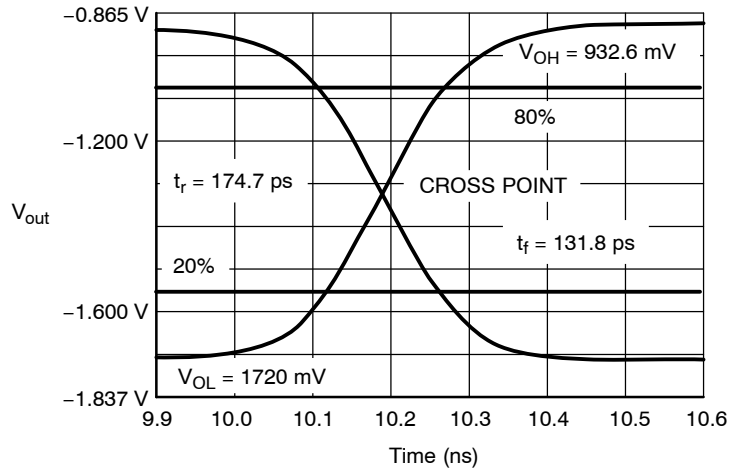


Figure 29. Typical Generic Output Waveform

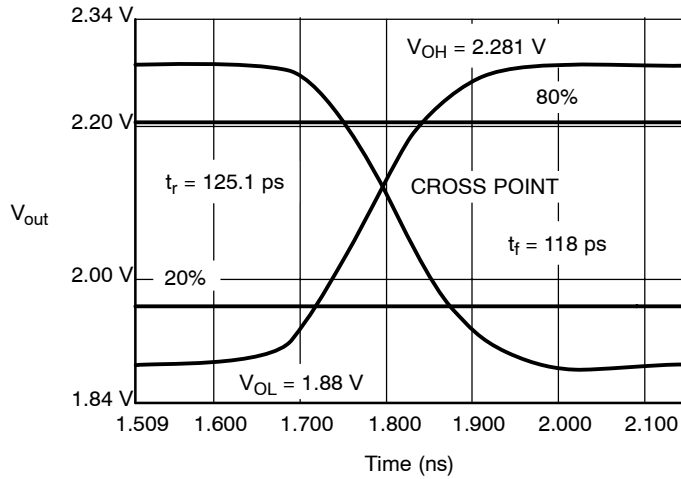


Figure 30. OBUF09 Reduced Swing Output Waveform (EP40/140)

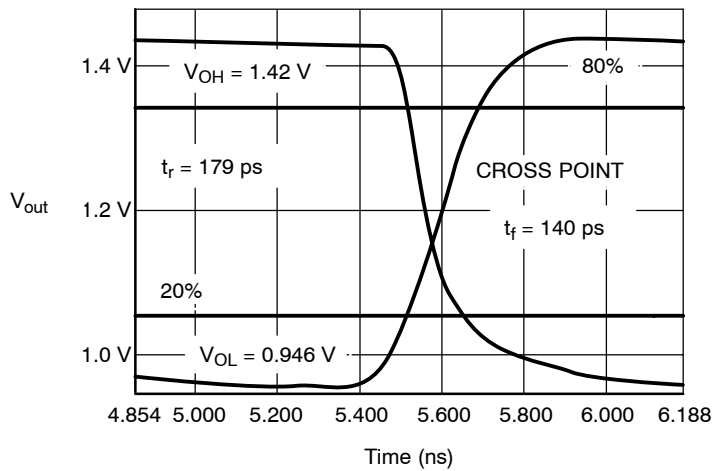


Figure 31. LVDS Output Waveform (EP210's)

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***** Transistor and Diodes Nominal SPICE Models* *****


```
*****
.MODEL TNA NPN (IS=8.12e-18 BF=192 NF=1 VAF=75.6 IKF=1.49e-02
+ ISE=9.14e-17 NE=2 BR=15.8 VAR=2.76 IKR=2.2e-03 ISC=2.62e-16
+ NC=1.578 RB=327 IRB=4.8e-05 RBM=0.001 RE=10 RC=15 CJE=2.0e-14
+ VJE=.8867 MJE=.2868 TF=9.02e-12 ITF=7.6e-03 XTF=2.8 VTF=3.4 PTF=41.56 TR=1NS
+ CJC=5.6e-15 VJC=.6324 MJC=.3006 XCJC=.3 CJS=4.8e-15 VJS=.4193 MJS=.2563
+ EG=1.119 XTI=3.999 XTB=0.8826 FC=0.9)
*****
.MODEL TNB NPN (IS=2.71e-17 BF=172 NF=1 VAF=71.4 IKF=4.38e-02
+ ISE=1.33e-15 NE=2 BR=17.9 VAR=2.76 IKR=3.0e-03 ISC=2.22e-16
+ NC=1.578 RB=67 IRB=6.47e-05 RBM=0.001 RE=3 RC=4 CJE=5.09e-14
+ VJE=.8867 MJE=.2868 TF=9.02e-12 ITF=2.53e-02 XTF=2.8 VTF=3.4 PTF=41.56 TR=1NS
+ CJC=20.6e-15 VJC=.6324 MJC=.3006 XCJC=.3 CJS=1.7e-14 VJS=.4193 MJS=.2563
+ EG=1.119 XTI=3.999 XTB=0.8826 FC=0.9)
*****
.MODEL TNC NPN (IS=6.55e-17 BF=103 NF=1 VAF=90 IKF=2.91e-01
+ ISE=8.85e-15 NE=2 BR=15.7 NR=1 VAR=3.82 IKR=2.01e-02 ISC=1.48e-15
+ NC=2 RB=10.5 IRB=4.39e-04 RBM=0.29 RE=0.351 RC=9 CJE=3.5e-13
+ VJE=.8167 MJE=.1973 TF=8.99e-12 ITF=1.3e-01 XTF=5.67 VTF=1.86 PTF=41.43 TR=6.405e-10
+ CJC=1.4e-13 VJC=.6401 MJC=.2674 XCJC=1 CJS=9.3e-14 VJS=.5002 MJS=.1706
+ EG=1.135 XTI=4.177 XTB=0.6322 FC=0.961)
*****
.MODEL TND NPN (IS=1.36e-17 BF=180 NF=1 VAF=87.6 IKF=2.19e-02
+ ISE=6.65e-16 NE=2 BR=16.9 VAR=2.76 IKR=1.5e-03 ISC=1.11e-16
+ NC=1.578 RB=136 IRB=3.24e-05 RBM=0.001 RE=6 RC=8 CJE=1.02e-13
+ VJE=.8867 MJE=.2868 TF=9.02e-12 ITF=1.27e-02 XTF=2.8 VTF=3.4 PTF=41.56 TR=1NS
+ CJC=10.3e-15 VJC=.6324 MJC=.3006 XCJC=.3 CJS=9.94e-15 VJS=.4193 MJS=.2563
+ EG=1.119 XTI=3.999 XTB=0.8826 FC=0.9)
*****
.MODEL TNE NPN (IS=2.68e-18 BF=223 NF=1 VAF=56.0 IKF=3.96e-03
+ ISE=3.07e-17 NE=2 BR=13.9 VAR=2.76 IKR=7.23e-04 ISC=6.08e-17
+ NC=1.578 RB=386 IRB=1.3e-05 RBM=0.001 RE=26 RC=28 CJE=6.0e-15
+ VJE=.8867 MJE=.2868 TF=9.02PS ITF=2.6e-03 XTF=2.8 VTF=3.4 PTF=41.56 TR=1NS
+ CJC=3.4e-15 VJC=.6324 MJC=.3006 XCJC=.3 CJS=3.4e-15 VJS=.4193 MJS=.2563
+ EG=1.119 XTI=3.999 XTB=0.8826 FC=0.9)
*****
.MODEL ESDM D (IS=1.55E-14 CJO=160fF RS=12 VJ=.58 M=.25 BV=9)
*****
.MODEL ESDS D (IS=1.55E-14 CJO=29fF VJ=.624 M=.571)
*****
*SPICE MODELS 4.5
```

AND8009/D

APPENDIX: PACKAGE RLC MODELS

	Package	R (Ω)	L (nH)	C (pF)
1	SOIC-8		1.5	0.188
2	TSSOP-8	0.048	1.9	0.089
3	SOIC-20 W	0.136	3.04	0.158
4	TSSOP-20	0.033	1.76	0.98
5	QFN-24	0.055	1.29	0.05
6	LQFP-32	0.67	2.38	0.13
7	LQFP-52	0.88	3.3	0.072
8	LQFP-64	0.10	0.67	0.05
9	QFN-16	0.039	0.75	0.13
10	QFN-32	0.42	1.39	0.142
11	TSSOP-10	0.048	1.9	0.089
12	SOIC-16	0.152	2.714	0.364
13	TSSOP-16	0.044	0.82	0.41

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